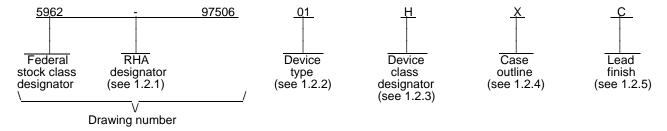
								R	EVISI	ONS										
LTR					D	ESCR	IPTIO	N					DA ⁻	TE (YF	R-MO-	DA)		APPR	OVED)
А	Corre	ection	s to ta	ble I.										98-0	3-23		K. A. Cottongim			
В	Add device type 02.										98-03-23 99-10-08			Ray Monnin						
	Editorial corrections to tables I, III, and figures 1, 2, 3, 4. Up													-						
С		orial co ving bo			tables	I, III,	and fig	gures '	1, 2, 3,	, 4. Սր	odate			03-0	3-31		Ra	aymon	a ivion	nın
REV	C 35	C 36	C 37	C 38	C 39	C 40	C 41	C 42	C 43	C 44	C 45	C 46	C 47	C 48	C 49	C 50	C 51			
SHEET	C 35 C	C 36 C	C 37	C 38	C 39	C 40 C	C 41 C	C 42 C	C 43 C	C 44 C	C 45 C	C 46 C	C 47 C	C 48 C	C 49 C	C 50 C	C 51 C	C	С	С
SHEET REV	35	36	37	38	39	40	41	42	43	44	45	46	47	48	49	50	51	C 32	C 33	C 34
SHEET REV SHEET	35 C 15	36 C	37 C	38 C	39 C 19	40 C	41 C	42 C	43 C	44 C	45 C	46 C	47 C	48 C	49 C	50 C	51 C			
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A	35 C 15	36 C	37 C	38 C 18 RE\ SHE	39 C 19	40 C 20 D BY	41 C 21 C	42 C 22	43 C 23	44 C 24	45 C 25 C	46 C 26 C	47 C 27 C 7	48 C 28 C 8	49 C 29 C 9	50 C 30 C 10	51 C 31 C	32 C 12	33 C 13	34
SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STAN	35 C 15	36 C 16	37 C	38 C 18 RE\ SHE PRE Gai	39 C 19 / EET	40 C 20 D BY	41 C 21 C	42 C 22 C	43 C 23 C	44 C 24 C	45 C 25 C	46 C 26 C 6	47 C 27 C 7 SE SI POS	48 C 28 C 8 JPPL T OF BUS	49 C 29 C 9 Y CE FICE	50 C 30 C 10	51 C 31 C 11 S COL 3990 216-56	32 C 12	33 C 13	3. C
SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STAN MICRO DRA	35 C 15 15 NDAR OCIRC WINC RAWIN	36 C 16 16 SUIT G	37 C	38 C 18 RE\ SHE PRE Gai CHE Mic	39 C 19 / EET PARE ry Zah	D BY n BY C. Jone	41 C 21 C 1	42 C 22 C 2	43 C 23 C	44 C 24 C 4	45 C 25 C 5	46 C 26 C 6 EFEN CC	47 C 27 C 7 SE SI POS DLUM http	48 C 28 C 8 JPPL T OF BUS,	49 C 29 C 9 Y CE FICE, OHIO	50 C 30 C 10 NTER BOX O 432 cc.dla	51 C 31 C 11 S COL 3990 216-50 a.mil	32 C 12	33 C 13 US	34 C
SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STAN MICRO DRA THIS DR AVAI FOR US	35 C 15 15 NDAR OCIRC WINC RAWIN ILABLE SE BY RTMEN ICIES (36 C 16 16 SUIT S IG IS E ALL JTS OF TH	37 C 17	38 C 18 RE\ SHE PRE Ga CHE Mic	39 C 19 / EET PARE ry Zah ECKED Chael C	D BY D BY D BY C. Jone	41 C 21 C 1	42 C 22 C 2	43 C 23 C 3	44 C 24 C 4	45 C 25 C 5 DE	46 C 26 C 6 EFEN CC	47 C 27 C 7 SE SI POS DLUM http	48 C 28 C 8 JPPL T OF BUS,	49 C 29 C 9 Y CE FICE, OHIO	50 C 30 C 10 NTER BOX O 432 cc.dla	51 C 31 C 11 S COL 3990 216-50 a.mil	32 C 12 LUMB	33 C 13 US	3. C
SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STAN MICRO DRA THIS DR AVAI FOR US DEPAR AND AGEN DEPARTMEN	35 C 15 15 NDAR OCIRC WINC RAWIN ILABLE SE BY RTMEN ICIES (JO SUIT S ALL SITS OF THORSES	37 C 17	38 C 18 RE\ SHE PRE Gai CHE Mic	39 C 19 / EET PARE ry Zah CKED chael C	D BY D BY C Jone ED BY C APPF 97-0	41 C 21 C 1	42 C 22 C 2	43 C 23 C 3	44 C 24 C 4 MIC (4) SU	45 C 25 C 5 DE	46 C 26 C 6 EFEN CC CIRC BIT)	47 C 27 C 7 SE SI POS DLUM http	48 C 28 C 8 JPPL T OF BUS, :://ww	49 C 29 C 9 Y CE FICE, OHIO	50 C 30 C 10 NTER BOX O 432 cc.dla	51 C 31 C 11 S COL 3990 216-56 a.mil	32 C 12 LUMB	33 C 13 US	, 1

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1. SCOPE

- 1.1 <u>Scope</u>. This drawing documents five product assurance classes as defined in paragraph 1.2.3 and MIL-PRF-38534. A choice of case outlines and lead finishes which are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of radiation hardness assurance levels are reflected in the PIN.
 - 1.2 PIN. The PIN shall be as shown in the following example:



- 1.2.1 <u>Radiation hardness assurance (RHA) designator</u>. RHA marked devices shall meet the MIL-PRF-38534 specified RHA levels and shall be marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.
 - 1.2.2 <u>Device type(s)</u>. The device type(s) identify the circuit function as follows:

Device type	Generic number	<u>Circuit function</u>
01	AD14060BF/QML-4	Quad digital signal processor, +5 V supply, 40 MHz, Twelve, 40 megabyte/s link ports (3 from each processor),
02	AD14060TF/QML-4	Four, 40 megabit/s independent serial ports (1 from each processor) Quad digital signal processor, +5 V supply, 40 MHz, Twelve, 40 megabyte/s link ports (3 from each processor), Four, 40 megabit/s independent serial ports (1 from each processor)

1.2.3 <u>Device class designator</u>. This device class designator shall be a single letter identifying the product assurance level. All levels are defined by the requirements of MIL-PRF-38534 and require QML Certification as well as qualification (Class H, K, and E) or QML Listing (Class G and D). The product assurance levels are as follows:

Device class	Device performance documentation
К	Highest reliability class available. This level is intended for use in space applications.
Н	Standard military quality class level. This level is intended for use in applications where non-space high reliability devices are required.
G	Reduced testing version of the standard military quality class. This level uses the Class H screening and In-Process Inspections with a possible limited temperature range, manufacturer specified incoming flow, and the manufacturer guarantees (but may not test) periodic and conformance inspections (Group A, B, C, and D).
Е	Designates devices which are based upon one of the other classes (K, H, or G) with exception(s) taken to the requirements of that class. These exception(s) must be specified in the device acquisition document; therefore the acquisition document should be reviewed to ensure that the exception(s) taken will not adversely affect system performance.
D	Manufacturer specified quality class. Quality level is defined by the manufacturers internal, QML certified flow. This product may have a limited temperature range.

1.2.4 <u>Case outline(s)</u>. The case outline(s) are as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	<u>Terminals</u>	Package style
Χ	See figure 1	308	Quad ceramic flat pack

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1.2.5 Lead finish. The lead finish shall be as specified in MIL-PRF-38534.

1.3 Absolute maximum ratings. 1/

Supply voltage (V _{DD})	-0.3 V dc to +7.0 V dc
Input voltage (V _{IN})	$-0.5 \text{ V dc to V}_{DD} + 0.5 \text{ V dc}$
Output voltage swing (V _{OUT})	$-0.3 \text{ V dc to V}_{DD} + 0.5 \text{ V dc}$
Load capacitance	200 pF
Junction temperature under bias (T _J)	+130°C
Junction-to-case temperature (θ _{JC})	0.36°C/W
Lead temperature soldering (5 seconds)	+280°C
Storage temperature	-65°C to +150°C

1.4 Recommended operating conditions.

Supply voltage (V _{DD})	+4.75 V dc to +5.25 V dc
Case operating temperature range (T _C):	
Device type 01	-40°C to +100°C
Device type 02	-55°C to +125°C

2. APPLICABLE DOCUMENTS

2.1 <u>Government specification, standards, and handbooks</u>. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those listed in the issue of the Department of Defense Index of Specifications and Standards (DoDISS) and supplement thereto, cited in the solicitation.

SPECIFICATION

DEPARTMENT OF DEFENSE

MIL-PRF-38534 - Hybrid Microcircuits, General Specification for.

STANDARDS

DEPARTMENT OF DEFENSE

MIL-STD-883 - Test Method Standard Microcircuits.

MIL-STD-1835 - Interface Standard Electronic Component Case Outlines.

HANDBOOKS

DEPARTMENT OF DEFENSE

MIL-HDBK-103 - List of Standard Microcircuit Drawings.
MIL-HDBK-780 - Standard Microcircuit Drawings.

WILL FIDDIN 700 Claridara Wilordon dan Drawingo.

(Unless otherwise indicated, copies of the specification, standards, and handbooks are available from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 <u>Order of precedence</u>. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

Stresses above the absolute maximum ratings may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.

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3. REQUIREMENTS

- 3.1 <u>Item requirements</u>. The individual item performance requirements for device classes D, E, G, H, and K shall be in accordance with MIL-PRF-38534. Compliance with MIL-PRF-38534 may include the performance of all tests herein or as designated in the device manufacturer's Quality Management (QM) plan or as designated for the applicable device class. Therefore, the tests and inspections herein may not be performed for the applicable device class (see MIL-PRF-38534). Furthermore, the manufacturer may take exceptions or use alternate methods to the tests and inspections herein and not perform them. However, the performance requirements as defined in MIL-PRF-38534 shall be met for the applicable device class.
- 3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38534 and herein.
 - 3.2.1 Case outline(s). The case outline(s) shall be in accordance with 1.2.4 herein and figure 1.
 - 3.2.2 Terminal connections. The terminal connections shall be as specified on figure 2.
 - 3.2.3 <u>Block diagram(s)</u>. The block diagram(s) shall be as specified on figure 3.
 - 3.2.4 Timing waveform(s). The timing waveform(s) shall be as specified on figure 4.
- 3.3 <u>Electrical performance characteristics</u>. Unless otherwise specified herein, the electrical performance characteristics are as specified in table I and shall apply over the full specified operating temperature range.
- 3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are defined in table I.
- 3.5 <u>Marking of device(s)</u>. Marking of device(s) shall be in accordance with MIL-PRF-38534. The device shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's vendor similar PIN may also be marked.
- 3.6 <u>Data</u>. In addition to the general performance requirements of MIL-PRF-38534, the manufacturer of the device described herein shall maintain the electrical test data (variables format) from the initial quality conformance inspection group A lot sample, for each device type listed herein. Also, the data should include a summary of all parameters manually tested, and for those which, if any, are guaranteed. This data shall be maintained under document revision level control by the manufacturer and be made available to the preparing activity (DSCC-VA) upon request.
- 3.7 <u>Certificate of compliance</u>. A certificate of compliance shall be required from a manufacturer in order to supply to this drawing. The certificate of compliance (original copy) submitted to DSCC-VA shall affirm that the manufacturer's product meets the performance requirements of MIL-PRF-38534 and herein.
- 3.8 <u>Certificate of conformance</u>. A certificate of conformance as required in MIL-PRF-38534 shall be provided with each lot of microcircuits delivered to this drawing.

4. QUALITY ASSURANCE PROVISIONS

- 4.1 <u>Sampling and inspection</u>. Sampling and inspection procedures shall be in accordance with MIL-PRF-38534 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.
 - 4.2 Screening. Screening shall be in accordance with MIL-PRF-38534. The following additional criteria shall apply:
 - a. Burn-in test, method 1015 of MIL-STD-883.
 - (1) Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to either DSCC-VA or the acquiring activity upon request. Also, the test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.
 - (2) T_C as specified in accordance with table I of method 1015 of MIL-STD-883.

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- b. Interim and final electrical test parameters shall be as specified in table II herein, except interim electrical parameter tests prior to burn-in are optional at the discretion of the manufacturer.
 - (1) Static supply current (I_{DDq}).

 Checks that current draw is not grossly excessive. Current exceeding 1.3 amperes on the module indicates failure. Normal measured current is about 0.5 amperes.
 - (2) Interconnects.

Checks for electrical continuity through the package leads and wire bonds, along with continuity of internal wiring within the module.

(3) Single processor functional.

A collection of test routines perform a rudimentary check of the basic functionally of each individual processor. The following individual processor units are tested: DAGs 1 and 2, timer, program sequencer, PX register, multiplier, data register file, shifter, ALU, link ports, serial ports, DMA, IOP registers, and memory.

(a) Serial port test.

This routine uses internal loopback to test basic operation of serial port 0 and serial port 1, by transmitting and receiving 16-bit words. In addition, the COMPare operation of the ALU and BitSET operation of the shifter are tested. Serial ports are tested at a clock rate of 10 MHz.

(b) Computation routine.

The routine tests basic operation of the ALU through ADD, SUBTRACT, and COMPare functions. In addition, the multiplier and DAGs are tested using floating point multiply and load/write functions, while the shifter is tested with a BitSET function. All operations use 32-bit words.

(c) Link routine

Using 32-bit data and internal memory to memory receive, basic operation of Link buffers 0 - 5 is tested. In addition, the ALU, COMPare, and shifter BitSET functions are tested.

(d) PX routine.

This routine tests basic operation of the PX register and short word addressing. The PX register is loaded with a 48-bit word, then the PX is read into memory. Short word addressing is used to read back, in 16-bit word segments, the 48-bit word from memory. In addition, the ALU, COMPare, and shifter BitSET functions are tested.

(e) Timer routine.

This routine will count down the timer until $t_{COUNT} = 0$, at which time an interrupt will occur, followed by a return to the code. This test will verify operation of the program sequencer, timer, ALU, COMPare function, and shifter BitSET function.

- (4) Multiprocessor functional.
 - (a) Interprocessor links: all tested using 2 times the clock rate (80 MHz).
 - (b) Multiprocessor memory space: each processor accesses and checks memory of the other three processors.
- c. Final electrical test parameters shall be as specified in table II herein.

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	T	ABLE I. Electrical performance	e characteristic	: <u>s</u> .			
Test	Symbol	Conditions 1/	Group A	Device	Limits		Unit
		unless otherwise specified	subgroups	type	Min	Max	
High level input voltage 2/	V _{IH1}	V _{DD} = +5.25 V dc	1,2,3	01,02	2.0		V
High level input voltage 3/	V _{IH2}	V _{DD} = +5.25 V dc	1,2,3	01,02	2.2		V
Low level input voltage 2/3/	V _{IL}	$V_{DD} = +4.75 \text{ V dc}$	1,2,3	01,02		0.8	V
High level output voltage <u>4</u> /	V _{OH}	$V_{DD} = +4.75 \text{ V dc}, \ \underline{5}/$ $I_{OH} = -2.0 \text{ mA}$	1,2,3	01,02	4.1		V
Low level output voltage <u>4</u> /	V _{OL}	$V_{DD} = +4.75 \text{ V dc}, \ \underline{5}/$ $I_{OL} = 4.0 \text{ mA}$	1,2,3	01,02		0.4	V
High level input current 6/ 7/ 8/	Іін	V_{DD} = +5.25 V dc, V_{IN} = $V_{DD}MAX$	1,2,3	01,02		10	μА
High level input current 8/ 9/ 10/	I _{IHx4}	V_{DD} = +5.25 V dc, V_{IN} = $V_{DD}MAX$	1,2,3	01,02		40	μА
Low level input current 6/	I _{IL}	$V_{DD} = +5.25 \text{ V dc}, V_{IN} = 0 \text{ V}$	1,2,3	01,02		10	μΑ
Low level input current 9/	I _{ILx4}	$V_{DD} = +5.25 \text{ V dc}, V_{IN} = 0 \text{ V}$	1,2,3	01,02		40	μА
Low level input current 7/	I _{ILP}	$V_{DD} = +5.25 \text{ V dc}, V_{IN} = 0 \text{ V}$	1,2,3	01,02		150	μА
Low level input current 8/ 10/	I _{ILPx4}	$V_{DD} = +5.25 \text{ V dc}, V_{IN} = 0 \text{ V}$	1,2,3	01,02		600	μΑ
Three state leakage current 11/ 12/ 13/ 14/	I _{OZH}	V_{DD} = +5.25 V dc, V_{IN} = $V_{DD}MAX$	1,2,3	01,02		10	μΑ
Three state leakage current 15/ 16/	I _{OZHx4}	V_{DD} = +5.25 V dc, V_{IN} = $V_{DD}MAX$	1,2,3	01,02		40	μА
Three state leakage current 11/17/	I _{OZL}	$V_{DD} = +5.25 \text{ V dc}, V_{IN} = 0 \text{ V}$	1,2,3	01,02		10	μΑ
Three state leakage current 15/	I _{OZLx4}	$V_{DD} = +5.25 \text{ V dc}, V_{IN} = 0 \text{ V}$	1,2,3	01,02		40	μΑ
Three state leakage current 17/	I _{OZHP}	V_{DD} = +5.25 V dc, V_{IN} = $V_{DD}MAX$	1,2,3	01,02		350	μΑ
Three state leakage current 14/	I _{OZLC}	$V_{DD} = +5.25 \text{ V dc}, V_{IN} = 0 \text{ V}$	1,2,3	01,02		1.5	mA
Three state leakage current 18/ See footnotes at end of table.	I _{OZLA}	$V_{DD} = +5.25 \text{ V dc}, V_{IN} = 2 \text{ V}$	1,2,3	01,02		350	μΑ

See footnotes at end of tal	ole.
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	TABLE	I. Electrical performar	nce chara	acteristics	- Con	tinued.			
Test	Symbol	Conditions <u>1</u> unless otherwise sp		Group A subgrou		Device type		nits	Unit
Three state leakage current 13/	I _{OZLAR}	V _{DD} = +5.25 V dc, V ₁	_{IN} = 0 V	1,2,3	3	01,02	Min	4.2	mA
Three state leakage current 12/	I _{OZLS}	V _{DD} = +5.25 V dc, V ₁	_{IN} = 0 V	1,2,3	3	01,02		150	μА
Three state leakage current 16/	I _{OZLSx4}	V _{DD} = +5.25 V dc, V _I	_{IN} = 0 V	1,2,3	3	01,02		600	μΑ
Supply current (internal) <u>19</u> /	I _{DDIN}	$t_{CK} = 25 \text{ ns}, V_{DD} = M$	AX	1,2,3	3	01,02		2.92	А
Supply current (idle) 20/	I _{DDIDLE}	V _{DD} = max		1,2,3	, [01		800	mA
						02		1200	
Input capacitance	C _{IN}	$f = 1 \text{ MHz}, T_C = +25^{\circ}$ $V_{IN} = 2.5 \text{ V dc}$	°C,			01,02	<u>2</u>	1/	
Functional tests		See 4.3.1.c		7,8		01,02			
Clock Input Timing Requirem	nents	Ι							
CLKIN period	t _{CK}	See figure 4.		9,10,1	1	01,02	25	100	ns
CLKIN width low	t _{CKL}						7		
CLKIN width high	t _{CKH}						5		
CLKIN rise/fall (0.4 V - 2.0 V)	t _{CKRF}							3	
Reset Timing Requirements	1	T		Т	1			1	ı
RESET pulse width low 23/	t _{WRST}	See figure 4. 22/		9,10,1	1	01,02	4t _{CK}		ns
RESET setup before CLKIN high 24/	t _{SRST}						14+DT/2	t _{CK}	
Interrupts Timing Requireme	nts				1				
IRQ2-0 setup before CLKIN high 25/	t _{SIR}	See figure 4. 22/		9,10,1	1	01,02	18+3DT/4		ns
IRQ2-0 hold before CLKIN high 25/	t _{HIR}							11.5+3DT/4	
IRQ2-0 width pulse 26/	t _{IPW}						2+t _{CK}		
See footnotes at end of table.	1	1		<u> </u>					<u> </u>
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	TABLE	I. Electrical performan	ice chara	acteristics	- Con	itinued.			
Test	Symbol	Conditions <u>1</u> , unless otherwise sp		Group A subgrou		Device type	Lin	nits	Unit
Timer Switching Characteris	tics						Min	Max	
CLKIN high to TIMEXP	t _{DTEX}	See figure 4. 22/		9,10,1	1	01,02		16	ns
FLAGS Timing and Switching	g Characte	ristics 					<u> </u>		
FLAG2-0 _{IN} setup before CLKIN high <u>27</u> /	t _{SFI}	See figure 4. 22/		9,10,1	1	01,02	8+5DT/16		ns
FLAG2-0 _{IN} hold after CLKIN high <u>27</u> /	t _{HFI}						0.5 - 5DT/16		
F <u>LA</u> G <u>2-</u> 0 _{IN} delay after RD/WR low <u>27</u> /	t _{DWRFI}							4.5+7DT/16	
FLAG2-0 _{IN} hold after RD/WR deasserted <u>27</u> /	t _{HFIWR}						0.5		
FLAG2-0 _{OUT} delay after CLKIN high	t _{DFO}							17	
FLAG2-0 _{OUT} hold after CLKIN high	t _{HFO}						4		
CLKIN high to FLAG2-0 _{OUT} enable	t _{DFOE}						3		
CLKIN high to FLAG2-0 _{OUT}	t _{DFOD}							15	
Memory Read - Bus Master T	iming and	Switching Requirement	ents				1		
Address delay to data valid 29/ 30/	t _{DAD}	See figure 4. 22/ 28	<u>3</u> /	9,10,1	1	01,02		17.5+DT+W	ns
RD low to data valid 29/	t _{DRLD}							11.5+5DT /D+W	
Data hold from address 31/	t _{HDA}						1		
Data hold from RD high 31/	t _{HDRH}						2.5		
ACK delay from address 30/ 32/	t _{DAAK}							13.5+7DT /8+W	
ACK delay from RD low 31/	t _{DSAK}							7.5+DT /2+W	
See footnotes at end of table.		-			_ 				
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	TABLE	I. Electrical performan	ce chara	cteristics -	Continue	d.			
Test	Symbol	Conditions 1/unless otherwise spo		Group A subgroup	Devi	се	Lir	mits	Unit
Memory Read - Bus Master T	iming and	Switching Requireme	ents - Co	ontinued.			Min	Max	
Address hold after RD high	t _{DRHA}	See figure 4. 22/ 28		9,10,11	1 01,0	12	-0.5+H		ns
Address to RD low 30/	t _{DARL}		2	0,10,11		,_	1.5+3DT /8		
RD pulse width	t _{RW}						12.5+5DT /8+W		
RD high to WR, RD, DMAGx low	t _{RWR}						8+3DT /8+HI		
Address setup before ADRCLK high 30/	tsadadc						-0.5+DT/4		
Memory Write - Bus Master T	iming and	Switching Requireme	ents						I
ACK delay from address selects 30/ 32/	t _{DAAK}	See figure 4. 22/ 28	<u>3</u> /	9,10,11	1 01,0)2		13.5+7DT /8+W	ns
ACK delay from WR low 32/	t _{DSAK}							8+DT /2+W	
Address, selects to WR deasserted 30/	t _{DAWH}						16.5+15DT /16+W		
Address, selects to WR low 30/	t _{DAWL}						2.5+3DT/8		
WR pulse width	t _{ww}						12+9DT /16+W		
Data setup before WR high	t _{DDWH}						6.5+DT /2+W		
Address hold after WR deasserted	t _{DWHA}						0+DT /16+H		
Data disabled after WR deasserted 33/	t _{DATRWH}						0.5+DT /16+H	6.5+DT /16+H	
WR high to WR, RD, DMAGx low	t _{WWR}						8+7DT /16+H		
D <u>ata</u> disable before WR or RD low	t _{DDWR}						4.5+3DT /8+I		
See footnotes at end of table.									
STAN MICROCIRCU	DARD JIT DRAV	VING	SIZ	ZE A				5962-97	506
DEFENSE SUPPLY (COLUMBUS, O					REVISION	C LTE	VEL	SHEET 9	

Test	Symbol	Conditions 1/	Group A	Device	Lim	nits	Unit
		unless otherwise specified	subgroups	type	Min	Max	
Memory Write - Bus Master T	iming and	Switching Requirements - Co	ontinued.	I			
WR low to data enabled	t _{WDE}	See figure 4. 22/ 28/	9,10,11	01,02	-1.5+DT/16		ns
Address, selects to ADRCLK high 30/	t _{SADADC}				0.5+DT/4		
Synchronous Read/Write - Bu	us Master 1	Fiming and Switching Requir	ements	1		ı	
Data setup before CLKIN	t _{SSDATI}	See figure 4. 22/ 28/	9,10,11	01,02	3+DT/8		ns
Data hold after CLKIN	t _{HSDATI}				4-DT/8		
A <u>CK</u> d <u>elay</u> a <u>fter</u> address, MSx, SW, BMS <u>30</u> / <u>32</u> /	t _{DAAK}					13.5+7DT /8+W	
ACK setup before CLKIN 32/	t _{SACKC}				6.5+DT/4		
ACK hold after CLKIN	t _{HACKC}				-0.5-DT/4		
Address, MSx, BMS, SW, delay after CLKIN 30/	t _{DADRO}					8-DT/8	
Address, MSx, BMS, SW, hold after CLKIN 30/	t _{HADRO}				-1-DT/8		
PAGE delay after CLKIN	t _{DPGC}				9+DT/8	17+DT/8	
RD high delay after CLKIN	t _{DRDO}				-2-DT/8	5-DT/8	
WR high delay after CLKIN	t _{DWRO}				-3-3DT /16	5-3DT /16	
RD/WR low delay after CLKIN	t _{DRWL}				8+DT/4	13.5+DT/4	
Data delay after CLKIN	t _{SDDATO}			01		20+5DT /16	
				02		20.5+5DT /16	

CTANDADD	SIZE		
STANDARD MICROCIRCUIT DRAWING	Α		5962-97506
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000		REVISION LEVEL C	SHEET 10

	TABLE	I. Electrical performance ch	aracteristics -	Continued.			
Test	Symbol	Conditions 1/ unless otherwise specifie	Group A	Device type	Lir	mits	Unit
Synchronous Read/Write - Bu	us Mastor 7	·			Min	Max	
Data disable after CLKIN 33/	t _{DATTR}	See figure 4. <u>22</u> / <u>28</u> /	9,10,11	01,02	0-DT/8	8-DT/8	ns
ADRCLK delay after CLKIN	t _{DADCCK}				4+DT/8	11+DT/8	
ADRCLK period	t _{ADRCK}				t _{CK}		
ADRCLK width high	t _{ADRCKH}				(t _{CK} /2-2)		
ADRCLK width low	t _{ADRCKL}				(t _{CK} /2-2)		
Synchronous Read/Write - Bu	us Slave Ti I	ming and Switching Requ	irements				1
Address, SW setup before CLKIN	t _{SADRI}	See figure 4. 22/ 28/	9,10,11	01,02	15.5+DT /2		ns
Address, SW hold before CLKIN	t _{HADRI}					4.5+DT/2	
 RD/WR low setup before CLKIN <u>34</u> /	t _{SRWLI}				9.5+5DT /16		
RD/WR low hold after CLKIN	t _{HRWLI}			01	-3.5-5DT /16	8+7DT /16	
				02	-3-5DT /16	8+7DT /16	
RD/WR pulse high	t _{RWHPI}			01,02	3		
Data setup before WR high	t _{SDATWH}				5.5		
Data hold after WR high	t _{HDATWH}				1.5		
Data delay after CLKIN	t _{SDDATO}			01		20+5DT /16	
				02		20.5+5DT /16	
Data disable after CLKIN 33/	t _{DATTR}			01,02	0-DT/8	8-DT/8	
ACK delay after address SW 35/	t _{DACKAD}					10	
ACK disable after CLKIN 35/ See footnotes at end of table.	t _{ACKTR}				-1-DT/8	7-DT/8	
Gee rootholes at end of table.							
STAN MICROCIRCU	DARD JIT DRAV	VING	SIZE A			5962-975	506
DEFENSE SUPPLY (COLUMBUS, O	CENTER CO	OLUMBUS	R	EVISION LE C	VEL	SHEET 11	

	TABLE I	. Electrical performance	e characteri	i <u>stics</u> - Cor	ntinued.			
Test	Symbol	Conditions <u>1/</u> unless otherwise spec		oup A ogroups	Device type	Lin	nits	Unit
						Min	Max	
Multiprocessor Bus Request	and Host F	Request Timing and Sw	vitching Re	equiremen	its		1	
HBG low to RD/WR/CS, valid	t _{HBGRCSV}	See figure 4. 22/ 28/	9	9,10,11	01,02		19.5+5DT /4	ns
HBR setup before CLKIN <u>37/</u>	t _{SHBRI}					20+3DT/4		
HBR hold before CLKIN 37/	t _{HHBRI}						13.5+3DT /4	
HBG setup before CLKIN	t _{SHBGI}					13+DT/2		
HBG hold before CLKIN high	t _{HHBGI}			ì	01		5.5+DT/2	
					02		5.25+DT/2	
BRx, CPA setup before CLKIN high <u>38</u> /	t _{SBRI}				01,02	13+DT/2		
BRx, CPA hold before CLKIN high	t _{HBRI}						5.5+DT/2	
RPBA setup before CLKIN	t _{SRPBAI}					21+3DT/4		
RPBA hold before CLKIN	t _{HRPBAI}						11.5+3DT/4	
HBG delay after CLKIN	t _{DHBGO}						8-DT/8	
HBG hold after CLKIN	t _{ннвдо}					-2-DT/8		
BRx delay after CLKIN	t _{DBRO}						8-DT/8	
BRx hold after CLKIN	t _{HBRO}					-2-DT/8		
CPA low delay after CLKIN	t _{DCPAO}						9-DT/8	
CPA disable after CLKIN	t _{TRCPA}					-2-DT/8	5.5-DT/8	
REDY <u>(O</u> /D) or <u>(A/</u> D) low from CS and HBR low <u>39</u> /	t _{DRDYCS}						9.5	
REDY (O/D) disable or 39/ REDY (A/D) high from HBG	t _{TRDYHG}					40+27DT /16		
RED <u>Y (A</u> /D) disable from CS or HBR high <u>39</u> /	t _{ARDYTR}						11	
See footnotes at end of table.								
STAN MICROCIRCU	DARD JIT DRAV	VING	SIZE A				5962-975	06
DEFENSE SUPPLY (COLUMBUS, O	CENTER CO	OLUMBUS		REV	ISION LE	VEL S	SHEET 12	

	TABLE I.	Electrical performar	nce charac	cteristics -	Continued.			
Test	Symbol	Conditions unless otherwise s		Group A subgrou		L	imits	Unit
Asynchronous Read Cycle Ti	iming and S	witching Requireme	ents			Min	Max	
A <u>ddr</u> ess setup/CS low before RD low <u>40</u> /	tsadrdl	See figure 4. 22/ 2		9,10,11	01,02	0.5		ns
Addres <u>s h</u> old/CS hold low after RD	t _{HADRDH}					0.5		
RD/WR high width	t _{WRWH}					6		
— RD high delay after REDY (O/D) disable	t _{DRDHRDY}					0		
— RD high delay after REDY (A/D) disable	t _{DRDHRDY}					0		
Data valid before REDY disable from low	t _{SDATRDY}					1.5		
REDY (O/D <u>) o</u> r (A/D) low delay after RD low	t _{DRDYRDL}						11	
REDY (O/D) or (A/D) low pulse width for read	t _{RDYPRD}					45+DT		
Data disable after RD high Asynchronous Write Cycle Ti	t _{HDARWH}	witching Requireme	ents			1.5	9	
CS low setup before WR low	tscswrl	See figure 4. 22/ 2	28/	9,10,11	01,02	0.5		ns
CS low hold after WR high	t _{HCSWRH}					0.5		
Address setup before WR high	t _{SADWRH}					5.5		
Address hold after WR high	t _{HADWRH}					2.5		
WR low width	t _{wwrl}					7		
RD/WR high width	twrwh					6		
WR high delay after REDY (O/D) or (A/D) disable	t _{DWRHRDY}					0.5		
Data setup before WR high See footnotes at end of table.	t _{SDATWH}					5.5		
STAN MICROCIRCU	IDARD JIT DRAW	ING	SIZ A				5962-97	7506
DEFENSE SUPPLY (COLUMBUS, O	CENTER CO	DLUMBUS		F	REVISION LE C	VEL	SHEET 13	

	TABLE I.	Electrical performan	nce charac	teristics	- Con	tinued.			
Test	Symbol	Conditions <u>f</u> unless otherwise s		Group /		Device type	Li	mits	Unit
Asynchronous Write Cycle Ti	iming and S	witching Requireme	ents - Cor	ntinued.			Min	Max	
					1 1	01.02	1.5		20
Data hold after WR high	t _{HDATWH}	See figure 4. 22/ 2	<u>20</u> /	9,10,1	'	01,02	1.5		ns
REDY (O/D) <u>or (A/D)</u> low delay after WR/CS low	t _{DRDYWRL}							11	
REDY (O/D) or (A/D) low pulse width for write	t _{RDYPWR}						15		
REDY (O/D) or (A/D) disable to CLKIN	t _{SRDYCK}						0+7DT /16	8+7DT /16	
Three State Timing - (Bus Ma	ster, Bus S	lave, HBR, SBTS) Ti	ming and	Switchi	ing Re	equireme	nts		
SBTS setup before CLKIN	t _{STSCK}	See figure 4. 22/ 2	<u>28</u> /	9,10,1	11	01,02	12.5+DT/2		ns
SBTS hold before CLKIN	thtsck							5.5+DT/2	
Address/select enable after CLKIN	t _{MIENA}						-1.5-DT/8		
Strobes enable after CLKIN <u>41</u> /	t _{MIENS}						-1.5-DT/8		
HBG enable after CLKIN	t _{MIENHG}						-1.5-DT/8		
Address select/disable after CLKIN	t _{MITRA}					01		1-DT/4	
						02		1.15-DT/4	
Strobes disable after CLKIN 41/	t _{MITRS}					01,02		2.5-DT/4	
HBG disable after CLKIN	t _{MITRHG}							3.0-DT/4	
Data enable after CLKIN 42/	t _{DATEN}						9+5DT/16		
Data disable after CLKIN 42/	t _{DATTR}						0-DT/8	8-DT/8	
ACK enable after CLKIN 42/	t _{ACKEN}						7.5+DT/4		
ACK disable after CLKIN 42/	tacktr						-1-DT/8	7-DT/8	
ADRCLK enable after CLKIN 42/	t _{ADCEN}						-2-DT/8		
See footnotes at end of table.									
STAN MICROCIRCU	DARD JIT DRAW	ING	SIZ A					5962-975	506
DEFENSE SUPPLY (COLUMBUS, O	CENTER CC	DLUMBUS			REVI	ISION LE C	VEL	SHEET 14	

	TABLE I.	Electrical performance	ce charac	<u>cteristics</u> - Co	ntinued.			
Test	Symbol	Conditions 1 unless otherwise sp		Group A subgroups	Device type		nits	Unit
Three State Timing - (Bus Ma	∣ ıster, Bus Sl	 ave, HBR, SBTS) Tir	ning and	Switching F	 Requireme	Min ents - Contin	Max ued.	
ADRCLK disable after CLKIN 42/	tadctr	See figure 4. 22/ 2	<u>8</u> /	9,10,11	01,02		9-DT/4	ns
Memory interface disable before HBG low 43/	t _{MTRHBG}					-1+DT/8		
Memor <u>y int</u> erface enable after HBG low <u>43</u> /	t _{MENHBG}					18.5+DT		
DMA Handshake Timing and	Switching F	Requirements						
DMARx low setup before CLKIN <u>44</u> /	t _{SDRLC}	See figure 4. 22/ 2	<u>8</u> /	9,10,11	01,02	5		ns
DMARx high setup before CLKIN <u>44</u> /	tsdrhc					5		
DMARx width low (nonsynchronous)	t _{WDR}					6		
Data setup after DMAGx low 45/	t _{SDATDGL}						9+5DT/8	
Data hold after DMAGx high	t _{HDATIDG}					2		
Data valid after DMARx high 45/	t _{DATDRH}						15.5+7DT /8	
DMAGx low edge to low edge	t _{DMARLL}					23+7DT/8		
DMAGx width high	t _{DMARH}					6		
DMAGx low delay after CLKIN	t _{DDGL}					9+DT/4	16+DT/4	
DMAGx high width	t _{WDGH}					6+3DT/8		
DMAGx low width	t _{WDGL}					12+5DT/8		
DMAGx high delay after CLKIN	t _{HDGC}					-2-DT/8	7-DT/8	
Data valid before DMAGx high 46/	t _{VDATDGH}					7.5+9DT/16		
See footnotes at end of table.								
STAN MICROCIRCU	DARD JIT DRAW	ING	SIZI A				5962-97	506
DEFENSE SUPPLY (COLUMBUS, O				RE	/ISION LE C	VEL	SHEET 15	

	TABLE I.	Electrical performa	nce charac	cteristics - C	ontinued.			
Test	Symbol	Conditions unless otherwise s		Group A subgroups	Device type	Lin	nits	Unit
DMA Handahaha Timin a and	O		•	Subgroups	Туре	Min	Max	
DMA Handshake Timing and	Switching	Requirements - Cor	itinuea.	<u> </u>				
Data disable after DMAGx high <u>33</u> /	t _{DATRDGH}	See figure 4. <u>22</u> /	<u>28</u> /	9,10,11	01,02	-1	7.5	ns
WR low before DMAGx low	t _{DGWRL}					-0.5	2.5	
DMAGx low before WR high	t _{DGWRH}					9.5+5DT /8+W		
WR high before DMAGx high	t _{DGWRR}					0.5+DT/16	3.5+DT/16	
RD low before DMAGx low	t _{DGRDL}				01	-0.25	2.5	
					02	-0.5	2.5	
RD low before DMAGx high	t _{DRDGH}				01,02	11+9DT /16+W		
RD high before DMAGx high	t _{DGRDR}					0	3.5	
D <u>MAGx</u> high to WR, RD, DMAGx low	t _{DGWR}					4.5+3DT /8+HI		
A <u>ddress</u> /select valid to DMAGx high	t _{DADGH}					16+DT		
A <u>ddress</u> /select hold after DMAGx high	t _{DDGHA}					-1.5		
Link Ports: 1 times Clock Spo	eed Operati	on, Receive Timing ⊺	and Swite	ching Requ	irements			
Data setup before LCLK low	t _{SLDCL}	See figure 4. 22/	<u>28</u> /	9,10,11	01,02	3.5		ns
Data hold after LCLK low	t _{HLDCL}					3		
LCLK period (1 x operation)	t _{LCLKIW}					t _{CK}		
LCLK width low	t _{LCLKRWL}					6		
LCLK width high	t _{LCLKRWH}					5		
LACK high delay after CLKIN high	t _{DLAHC}					18+DT/2	29.5+DT/2	
LACK low delay after CLKIN high 47/	t _{DLALC}					-3	13.5	
See footnotes at end of table.								
STAN MICROCIRCU	DARD	/ING	SIZ A				5962-975	506
DEFENSE SUPPLY (COLUMBUS, O	CENTER CC	DLUMBUS		RE	EVISION LE C	VEL	SHEET 16	

	TABLE I.	Electrical performance characteristics	cteristics - Cor	ntinued.			
_							
Test	Symbol	Conditions 1/ unless otherwise specified	Group A subgroups	Device type	Lim	nits	Unit
					Min	Max	
Link Ports: 1 times Clock Sp	eed Operati	on, Receive Timing and Swite	ching Require	ements -	Continued.	<u> </u>	
LACK enable from CLKIN	t _{ENDLK}	See figure 4. 22/ 28/	9,10,11	01,02	5+DT/2		ns
LACK disable from CLKIN	t _{TDLK}					21+DT/2	
Link Ports: 1 times Clock Sp	eed Operati	on, Transmit Timing and Swi	tching Requi	rements	1	1	
LACK setup before LCLK	t _{SLACH}	See figure 4. 22/ 28/	9,10,11	01	18		ns
high				02	19.25		
LACK hold after LCLK high	t _{HLACH}			01,02	-7		
LCLK delay after CLKIN	t _{DLCLK}			01		16.5	
(1 x operation)				02		17	
Data delay after LCLK high	t _{DLDCH}			01,02		3.5	
Data hold after LCLK high	tHLDCH				-3		
LCLK width low	t _{LCLKTWL}			01	(t _{CK} /2)-2	(t _{CK} /2)+2	
				02	(t _{CK} /2)-2	(t _{CK} /2)+2.25	
LCLK width high	t _{LCLKTWH}			01	(t _{CK} /2)-2	(t _{CK} /2)+2	
				02	(t _{CK} /2)-2.25	(t _{CK} /2)+2	
LCLK low delay after LACK high	t _{DLACLK}			01	(t _{CK} /2) +8.5	(3*t _{CK} /2) +17.5	
				02	(t _{CK} /2) +8.5	(3*t _{CK} /2) +18.5	
LDAT, LCLK enable after CLKIN	t _{ENDLK}			01,02	5+DT/2		
LDAT, LCLK disable after CLKIN	t _{TDLK}					21+DT/2	

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-97506
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	TABLE I.	Electrical performar	nce charac	<u>cteristics</u> - Co	ntinued.					
Test	Symbol	Conditions of unless otherwise s		Group A subgroups	Device type	Lir	mits	Unit		
			•			Min	Max			
Link Port Service Request In	terrupts: 1 t	imes and 2 times Sp	peed Ope	ration Timin	g Require	ments				
LACK/LCLK setup before CLKIN low <u>48</u> /	t _{SLCK}	See figure 4. 22/ 2	<u>28</u> /	9,10,11	01,02	10		ns		
LACK/LCLK hold after CLKIN low 48/	t _{HLCK}					2.5				
Link Ports: 2 times Clock Speed Operation, Receive Timing and Switching Requirements										
Data setup before LCLK low	t _{SLDCL}	See figure 4. 22/ 2	<u>28</u> /	9,10,11	01,02	2.75		ns		
Data hold after LCLK low	t _{HLDCL}					2.25				
LCLK period (2 x operation)	t _{LCLKIW}					t _{CK} /2				
LCLK width low	t _{LCLKRWL}				01	4.6				
					02	4.7				
LCLK width high	t _{LCLKRWH}				01,02	4.25				
LACK high delay after CLKIN high	t _{DLAHC}					18+DT/2	31.5+DT/2			
LACK low delay after CLKIN high 47/	t _{DLALC}					6	17.8			
Link Ports: 2 times Clock Spe	eed Operati	on, Transmit Timing │	and Swi	tching Requ	irements					
LACK setup before LCLK high	t _{SLACH}	See figure 4. 22/ 2	<u>28</u> /	9,10,11	01	20.25		ns		
					02	19.25				
LACK hold after LCLK high	t _{HLACH}				01,02	-6.5				
LCLK delay after CLKIN (2 x operation	t _{DLCLK}						9			
Data delay after LCLK high	t _{DLDCH}				01		3.25			
					02		3.35			
Data hold after LCLK high	t _{HLDCH}				01,02	-2				
See footnotes at end of table.										
	DARD	ING	SIZ A				5962-97	506		
MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000					/ISION LE	VEL	SHEET 18			

TABLE I. <u>Electrical performance characteristics</u> - Continued.									
Test	Symbol	Conditions gunless otherwise s		Group A subgroups	Device type	Lir	mits Max	Unit	
Link Ports: 2 times Clock Sp	eed Operation	on, Transmit Timing	and Swi	tching Req	uirements -				
LCLK width low	t _{LCLKTWL}	See figure 4. 22/ 2	<u>28</u> /	9,10,11	01,02	(t _{CK} /4)-1	(t _{CK} /4)+1.5	ns	
LCLK width high	t _{LCLKTWH}					(t _{CK} /4)-1.5	(t _{CK} /4)+1		
LCLK low delay after LACK high	t _{DLACLK}					(t _{CK} /4)+9	(3*t _{CK} /4)+17		
Link data setup skew 49/	t _{SLSK}						0.45 <u>50</u> /		
Link data hold skew 51/	t _{HLSK}						3.35		
Serial Ports: External Clock		uirements			1	1			
TFS/RFS setup before TCLK/RCLK <u>52</u> /	t _{SFSE}	See figure 4. <u>22</u> / <u>2</u>	<u>28</u> /	9,10,11	01,02	4		ns	
TFS/RFS hold after TCLK/RCLK <u>52</u> / <u>53</u> /	t _{HFSE}					4.5			
Receive data setup before RCLK <u>52</u> /	t _{SDRE}					1.5			
Receive data hold after RCLK <u>52</u> /	t _{HDRE}					4.5			
TCLK/RCLK width	t _{SCLKW}					9.5			
TCLK/RCLK period	t _{SCLK}					t _{CK}			
Serial Ports: Internal Clock T	iming Requ	irements				1	1		
TFS setup before TCLK: RFS setup before RCLK <u>52/</u>	t _{SFSI}	See figure 4. 22/ 2	<u>28</u> /	9,10,11	01,02	9.5		ns	
TFS/RFS hold after TCLK/RCLK <u>52</u> / <u>53</u> /	t _{HFSI}					1			
Receive data setup before RCLK <u>52</u> /	t _{SDRI}					4.5			
Receive data hold after RCLK 52/	t _{HDRI}					3			
See footnotes at end of table.									
STAN MICROCIRCU	DARD JIT DRAW	ING	SIZ A				5962-975	506	
DEFENSE SUPPLY (COLUMBUS, O	DLUMBUS		RE	EVISION LE C	VEL	SHEET 19			

TABLE I. <u>Electrical performance characteristics</u> - Continued.									
Test	Symbol	Conditions unless otherwise s		Group A subgroups	Device type	Lir	nits	Unit	
Serial Ports: External or Inte	rnal Clock S		-		31.	Min	Max		
Serial Ports. External or line	liai Clock 3	Witching Requirem	ents						
RFS delay after RCLK <u>54/</u> (internally generated RFS)	t _{DFSE}	See figure 4. 22/ 2	<u>28</u> /	9,10,11	01,02		14.5	ns	
RFS hold after RCLK <u>54</u> / (internally generated RFS)	t _{HOFSE}					2.5			
Serial Ports: External Clock Switching Requirements									
TFS delay after TCLK <u>54</u> / (internally generated TFS)	t _{DFSE}	See figure 4. <u>22</u> / <u>:</u>	<u>28</u> /	9,10,11	01,02		14.5	ns	
TFS hold after TCLK <u>54</u> / (internally generated TFS)	t _{HOFSE}					3			
Transmit data delay after TCLK <u>54</u> /	t _{DDTE}						17.5		
Transmit data hold after TCLK <u>54</u> /	t _{HDTE}					5			
Serial Ports: Internal Clock S	witching Re	equirements			1	T			
TFS delay after TCLK <u>54</u> / (internally generated TFS)	t _{DFSI}	See figure 4. <u>22</u> / <u>2</u>	<u>28</u> /	9,10,11	01,02		5	ns	
TFS hold after TCLK <u>54</u> / (internally generated TFS)	t _{HOFSI}					-1.5			
Transmit data delay after TCLK <u>54</u> /	t _{DDTI}						7.5		
Transmit data hold after TCLK <u>54</u> /	t _{HDTI}					-0.5			
TCLK/RCLK width	tsclkiw					(SCLK/2)-2	(SCLK/2)+2	,	
Serial Ports: Enable and Thre		itching Requiremen	ts				1(002102) F2	-1	
Data enable from external TCLK <u>54</u> /	t _{DDTEN}	See figure 4. <u>22</u> / 2		9,10,11	01,02	3.5		ns	
Data disable from external TCLK <u>54</u> /	t _{DDTTE}						12		
Data enable from internal TCLK <u>54</u> /	t _{DDTIN}					-0.5			
See footnotes at end of table.									
STAN MICROCIRCI	DARD JIT DRAW	/ING	SIZ A				5962-97	506	
DEFENSE SUPPLY (COLUMBUS, O		RE	EVISION LE C	VEL	SHEET 20				

TABLE I. Electrical performance characteristics - Continued.									
Test	Symbol	Conditions 1		Group A subgroups	Device type	Lir	mits	Unit	
Serial Ports: Enable and Thre	ee State Swi				71.	Min	Max		
Data disable from internal TCLK 54/	t _{DDTTI}	See figure 4. <u>22</u> / <u>2</u>		9,10,11	01,02		3	ns	
TCLK/RCLK delay from CLKIN	t _{DCLK}						23.5+3DT/8		
SPORT disable after CLKIN	t _{DPTR}						18.5		
Serial Ports: Gated SCLK wit									
TFS setup before CLKIN <u>55</u> /	t stfsck	See figure 4. 22/ 2	<u>8</u> /	9,10,11	01	5.5		ns	
					02	5.6			
TFS hold after CLKIN <u>55</u> / Serial Ports: External Late Fr	t _{HTFSCK}	witching Requireme	ents		01,02	(t _{CK} /2)+0.5			
Data disable from late external TFS or RFS with MCE = 1, MFD = 0 56/	t _{DDTLFSE}	See figure 4. 22/ 2		9,10,11	01,02		14.1	ns	
Data enable from late FS or MCE = 1, MFD = 0 56/	t _{DDTENFS}					3			
JTAG Test Access Port Emul	ation Timin	g and Switching Red	uiremen	ts					
TCLK period	t _{TCK}	See figure 4. 22/ 2	<u>8</u> /	9,10,11	01,02	tck		ns	
TDI, TMS, setup before TCK high	T _{STAP}					5			
TDI, TMS, hold after TCK high	T _{HTAP}					6			
Systems inputs setup before TCK low <u>57</u> /	tssys				01	7 8			
Systems inputs hold after TCK low <u>57</u> /	t _{HSYS}				01,02	18.5			
TRST pulse width	t _{TRSTW}					4t _{CK}			
TDO delay from TCK low before TCK low	t _{DTDO}						13.5		
Systems outputs delay after TCK low <u>58</u> /	t _{DSYS}						20		
See footnotes on next sheet.									
STAN MICROCIRCU	DARD JIT DRAW	ING	SIZ A				5962-975	506	
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000				RE	/ISION LE C	VEL	SHEET 21		

TABLE I. <u>Electrical performance characteristics</u> - Continued.

- 1/ Device type 01, $-40^{\circ}\text{C} \le T_{\text{C}} \le +100^{\circ}\text{C}$ and +4.75 V dc $\le V_{\text{DD}} \le +5.25 \text{ V}$ dc, unless otherwise specified. Device type 02, $-55^{\circ}\text{C} \le T_{\text{C}} \le +125^{\circ}\text{C}$ and +4.75 V dc $\le V_{\text{DD}} \le +5.25 \text{ V}$ dc, unless otherwise specified.
- 2/ Applies to input and bi-directional pins: DATA47-0, ADDR31-0, RD, WR, SW, ACK, SBTS, IRQy2-0, FLAGy0, FLAG1, FLAGy2, HBG, CSy, DMAR1, DMAR2, BR6-1, RPBA, CPAy, TFS0, TFSy1, RFS0, RFSy1, LyxDAT3-0, LyxCLK, LyxACK, EBOOTA, LBOOTA, EBOOTBCD, LBOOTBCD, BMSA, BMSBCD, TMS, TDI, TCK, HBR, DR0, DRy1, TCLK0, TCLKy1, RCLK0, RCLKy1. For the group of signals LyxDAT3-0, LyxCLK, and LyxACK, only Link Port 4 signals (Ly4DT3-0, Ly4CLK, and Ly4ACK) from each of the processors are tested at the module level. Link Ports 1, 2, and 3 are not DC tested at the module level, but are tested at the die level prior to assembly.
- 3/ Applies to input pins: CLKIN, RESET,TRST.
- 4/ Applies to output and bi-directional pins: DATA47-0, ADDR31-0, MS3-0, RD, WR, PAGE, ADRCLK, SW, ACK, FLAGy0, FLAG1, FLAGy2, TIMEXPy, HBG, REDY, DMAG1, DMAG2, BR6-1, CPAy, DTO, DTy1, TCLK0, TCLKy1, RCLK0, RCLKy1, TFS0, TFSy1, RFS0, RFSy1, LyxDAT3-0, LyxCLK, LyxACK, BMSA, BMSBCD, TDO, EMU. For the group of signals LyxDAT3-0, LyxCLK, and LyxACK, only Link Port 4 signals (Ly4DAT3-0, Ly4CLK, and Ly4ACK) from each of the processors are tested at the module level. Link Ports 1, 2, and 3 are not DC tested at the module level, but are tested at the die level prior to assembly.
- 5/ See "output drive currents" for typical drive current capabilities.
- 6/ Applies to input pins: IRQy2-0, CSy, EBOOTA, LBOOTA.
- 7/ Applies to input pins with internal pull-ups: DRy1, TDI.
- 8/ Individual signals tested to limits of $I_{IH} = 10 \mu A$ and $I_{ILP} = 150 \mu A$ at die level prior to assembly. At the module level, all eight DR0 and DRy1 inputs connected together are tested to limits of $I_{IH} = 80 \mu A$ and $I_{ILP} = 1200 \mu A$.
- 9/ Applies to bussed input pins: SBTS, HBR, DMAR1, DMAR2, RPBA, EBOOTBCD, LBOOTBCD, CLKIN, RESET, TCK.
- 10/ Applies to bussed input pins with internal pull-ups: DR0, TRST, TMS.
- 11/ Applies to three statable pins and bi-directional pins; FLAGy0, FLAGy2, BMSA, TDO, TFSy1, RFSy1. TFSy1 and RFSy1 are tested individually to the limits of $I_{OZH} = 10 \mu A$ and $I_{OZL} = 10 \mu A$ at die level. At the module level, eight pins connected together are tested to limits of $I_{OZH} = 80 \mu A$ and $I_{OZL} = 80 \mu A$.
- 12/ Applies to three statable pins with internal pull-ups: DTy1, TCLKy1, RCLKy1. Individual signals tested to limit of $I_{OZH} = 10 \mu A$ and $I_{OZLS} = 150 \mu A$ at die level. At the module level, eight serial port pins connected together are tested to limits of $I_{OZH} = 80 \mu A$ and $I_{OZLS} = 1200 \mu A$.
- 13/ Applies to ACK pin when pulled up. (Note that ACK is pulled up internally with a 2 kΩ resistor during reset in a multiprocessor system, when ID2-0 = 001 and another single processor is not requesting bus mastership.)
- 14/ Applies to CPAy pin.
- 15/ Applies to bussed three statable pins and bi-directional pins: DATA47-0, ADDR31-0, MS3-0, RD, WR, PAGE, ADRCLK, SW, ACK, FLAG1, HBG, REDY, DMAG1, DMAG2, BMSBCD, TFS0, RFS0, BR5, BR6, EMU. (Note that ACK is pulled up internally with a 2 kΩ resistor during reset in a multiprocessor system, when ID2-0 = 001 and another single processor is not requesting bus mastership.) HBG and EMU are not tested for leakage current. At the die level, component pins that make up TFS0 and RFS0 are tested to limits of I_{OZH} = 10 μA and I_{OZL} = 10 μA. At the module level, eight pins connected together are tested to limits of I_{OZL} = 80 μA and I_{OZL} = 80 μA.
- 16/ Applies to bussed three statable pins with internal pull-ups: DT0, TCLK0, RCLK0. At the module level, all eight DR0 and DRy1 inputs connected together are tested to limits of I_{OZH} = 80 μA and I_{OZLS} = 1200 μA.
- 17/ Applies to three statable pins with internal pull-downs: LyxDAT3-0, LyxCLK, LyxACK. Only Link Port 4 signals (Ly4DAT3-0, Ly4CLK, and Ly4ACK) from each of the processors are tested at the module level. Link Ports 1, 2, and 3 are not DC tested at the module level, but are tested at the die level prior to assembly.
- 18/ Applies to ACK pin when keeper latch enabled.
- 19/ Applies to V_{DD} pins. Conditions of operation: each processor executing radix-2 FFT butterfly with instruction in cache, one data operand fetched from cache each internal memory block, and one DMA transfer occurring from/to internal memory at t_{CK} = 25 ns. Total power dissipation has two components, one due to internal circuitry and one due to the switching of external output drivers: P_{TOTAL} = P_{INT} + P_{EXT}. Internal power dissipation is P_{INT} = I_{DDIN} x V_{DD}. The external component of total power dissipation is caused by the switching of output pins, and depends on: the number of pins that switch each cycle (O), the maximum frequency at which they can switch (f), the load capacitance per pin (C), the output voltage swing (V_{DD}): P_{EXT} = O x C x V_{DD}² x f. Address and data pins can switch at f = 1/ (2t_{CK}). WR can switch at 1/ t_{CK}. MSx pins switch at 1/ (2t_{CK}).
- $\underline{20}$ / Applies to V_{DD} pins. Idle denotes like device type state during execution of IDLE instruction.
- 21/ Not tested. Nominal value of 15 pF derived through RC measurement at design characterization.

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TABLE I. Electrical performance characteristics - Continued.

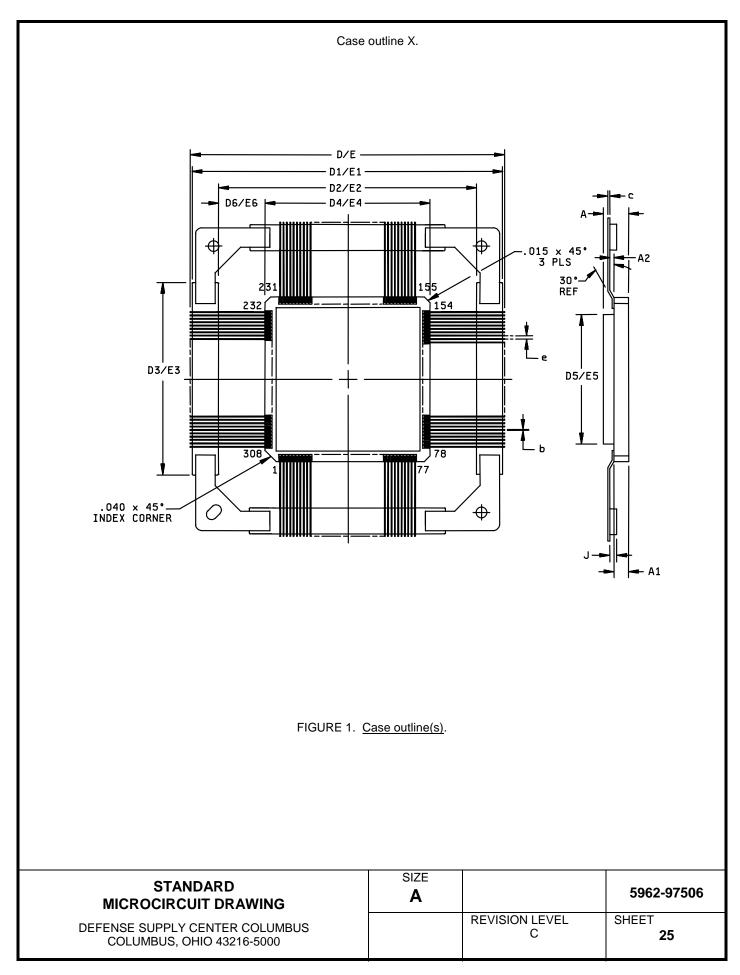
- 22/ Timing test limits are target limits for the module, based on calculated predictions only. The module is 100% production tested, and the test limits are guaranteed by design/analysis, and characterization testing (at T_A = 25°C) of the individual discrete microcontrollers. The limits shown are based on a CLKIN frequency of 40 MHz. DT is the difference between the actual CLKIN period and a CLKIN period of 25 ns: DT = t_{CK} 25 ns. Link and serial ports: all are 100% tested at die level, serial ports are 100% AC tested at module level, only Link Port 4 from each processor is AC tested at module level, then link and serial ports are DC tested at module level.
- 23/ Applies after the power-up sequence is complete. At power-up, the processor's internal phase-locked loop requires no more than 2000 CLKIN cycles while RESET is low, assuming stable V_{DD} and CLKIN (not including start-up time of external oscillator).
- 24/ Only required if multiple microcontrollers must come out of reset synchronous to CLKIN with program counters (PC) equal (i. e. for a SIMD system). Not required for multiple microcontrollers communicating over the shared bus (through the external port), because the bus arbitration logic synchronizes it self automatically after reset.
- 25/ Only required for IRQx recognition in the following cycle.
- 26/ Applies only if t_{SIR} and t_{HIR} requirements are not met.
- 27/ Flag inputs meeting these setup and hold times will affect conditional instructions in the following instruction cycle.
- 28/ W = (number of wait states specified in WAIT register) times t_{CK}. HI = t_{CK} (if an address hold cycle or bus idle cycle occurs, as specified in WAIT register; otherwise HI = 0). H = t_{CK} (if an address hold cycle occurs as specified in WAIT register; otherwise H = 0). I = t_{CK} (if bus idle cycle occurs, as specified in WAIT register; otherwise I = 0).
- 29/ Data delay/setup: User must meet tDAD or tDRLD or synchronous specification tSSDATI-
- 30/ For MSx, SW, and BMS, the falling edge is referenced.
- 31/ Data hold: User must meet t_{HDA} or t_{HDRH} or synchronous specification t_{HDATI}. To determine system hold time, the data output hold time in a particular system, first calculate t_{DECAY} = C_L ΔV / I_L. Choose ΔV to be the difference between the microcontroller's output voltage and the input threshold for the device requiring the hold. Typical ΔV is 0.4 volt. C_L is the total bus capacitance (per data line), and I_L is the total leakage or three state current (per data line). The hold time will be t_{DECAY} plus the minimum disable time (i. e. t_{HDWD} for the write cycle).
- 32/ ACK delay/setup: User must meet t_{DSAK} or t_{DAAK} or synchronous specification t_{SACKC}.
- 33/ To determine system hold time, the data output hold time in a particular system, first calculate $t_{DECAY} = C_L \Delta V / I_L$. Choose ΔV to be the difference between the microcontroller's output voltage and the input threshold for the device requiring the hold. Typical ΔV is 0.4 volt. C_L is the total bus capacitance (per data line), and I_L is the total leakage or three state current (per data line). The hold time will be t_{DECAY} plus the minimum disable time (i. e. t_{HDWD} for the write cycle).
- 34/ t_{SRWLI} (min) = 9.5 + 5DT/16, when multiprocessor memory space wait state (MMSWS bit in WAIT register) is disabled; when MMSWS is enabled, t_{SRWLI} (min) = 4 + DT/8.
- 35/ t_{DACKAD} is true only if the address and SW inputs have setup times (before CLKIN) greater than 10.5 + DT/8 and less than 18.5 + 3DT/4. If the address and SW inputs have setup times greater than 19 + 3DT/4, then ACK is valid 15 + DT/4 (max) after CLKIN. A slave that sees an address with a M field match will respond with ACK regardless of the state of MMSWS or strobes. A slave will three state ACK every cycle with tacktr.
- 36/ For first asynchronous access after HBR and CS asserted, ADDR31-0 must be a non-MMS value 1/2t_{CK} before RD or WR goes low or by t_{HBGRCSV} after HBG goes low. This is easily accomplished by driving an upper address signal high when HBG is asserted.
- 37/ Only required for recognition in the current cycle.
- 38/ CPA assertion must meet the setup to CLKIN; deassertion does not need to meet the setup to CLKIN.
- $\overline{39}$ / (O/D) = open d<u>rain</u>, (A/D) = active drain.
- 40/ Not required if RD and address are valid the Grown after HBG goes low. For first access after HBR asserted, ADDR31-0 must be a non-MMS value 1/2tck before RD or WR goes low or by the Grown accomplished by driving an upper address signal high when HBG is asserted. For address bits to be driven during asynchronous host accesses, see QML manufacturer.
- 41/ Strobes = RD, WR, SW, PAGE, and DMAG.
- 42/ In addition to bus master transition cycles, these specifications also apply to bus master and bus slave synchronous read/write.
- 43/ Memory interface = Address, RD, WR, MSx, SW, HBG, PAGE, DMAGx, and BMS (in EPROM boot mode).

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TABLE I. <u>Electrical performance characteristics</u> - Continued.

- 44/ Only required for recognition in the current cycle.
- 45/ t_{SDATDGL} is the data setup requirement if DMARx is not being used to hold off completion of a write. Otherwise, if DMARx low holds off completion of the write, the data can be driven t_{DATDRH} after DMARx is brought high.
- $\frac{46}{t_{VDATDGH}}$ is valid if DMARx is not being used to hold off completion of a read. If DMARx is used to prolong the read, then $t_{VDATDGH} = 7.5 + 9DT/16 + (n * t_{ck})$ where "n" equals the number of extra cycles that the access is prolonged.
- 47/ LACK will go low with t_{DLALC} relative to rising edge of LCLK after first nibble is received. LACK will not go low if the receivers link buffer is not about to fill.
- 48/ Only required for interrupt recognition in the current cycle.
- 49/ t_{SLSK} is the maximum delay that can be introduced in the transmission path of LDATA relative LCLK: t_{SLSK} = (t_{LCLKTWH} t_{DLDCH})min t_{SLDCL} max.
- 50/ If link port 2 is transmitter, t_{SLSK} = 0.28 ns. Because of this small margin, extreme care must be taken in system design. If adequate setup time cannot be assured, link port operation should be limited to 1X, or system CLKIN frequency should be reduced to increase the setup margin at 2X.
- 51/ thusk is the maximum delay that can be introduced in the transmission path of LCLK relative to LDATA: thusk = (tlclktwl thldch)min thldcl max.
- 52/ Reference to sample edge.
- 53/ RFS hold after RCK when MCE = 1, MFD = 0 is 0.5 ns minimum from drive edge. TFS hold after TCK for late external TFS is 0.5 ns minimum from drive edge.
- 54/ Reference to drive edge.
- 55/ Applies only to gated serial clock mode used for serial port system I/O in mesh multiprocessing systems.
- 56/ MCE = 1, TFS enable and TFS valid follow todtlese and todtenes.
- 57/ System inputs = DATA47-0, ADDR31-0, RD, WR, ACK, SBTS, SW, HBR, HBG, CS, DMAR1, DMAR2, BR6-1, RPBA, IRQ2-0, FLAG2,0, DR0, DR1, TCLK0, TCLK1, RCLK0, RCLK1, TFS0, TFS1, RFS0, RFS1, LxDAT3-0, LxCLK, LxACK, EBOOT, LBOOT, BMS, CLKIN, RESET.
- 58/ System outputs = DATA47-0, ADDR31-0, MS3-0, RD, WR, ACK, PAGE, ADRCLK, SW, HBG, REDY, DMAG1, DMAG2, BR6-1, CPA, FLAG2,0, TIMEXP, DT0, DT1, TCLK0, TCLK1, RCLK0, RCLK1, TFS0, TFS1, RFS0, RFS1, LxDAT3-0, LxCLK, LxACK, BMS.

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Case outline X - Continued.

Symbol	Millim	neters	Inc	hes
	Min	Max	Min	Max
А		4.06		.160
A1	2.11	2.57	.083	.101
A2	0.08	0.33	.003	.013
b	0.15	0.25	.006	.010
С	0.10	0.17	.004	.0065
D/E		77.47		3.050
D1/E1	75.95	76.45	2.990	3.010
D2/E2	68.96	69.72	2.715	2.745
D3/E3	57.66	59.18	2.270	2.330
D4/E4	51.77	52.37	2.038	2.062
D5/E5	47.88	48.13	1.885	1.895
D6/E6	8.38	8.89	.330	.350
е	0.64 BSC		.025	BSC
J		0.89		.035

NOTES:

- 1. The U.S. preferred system of measurement is the metric SI. This item was designed using inch-pound units of measurement. In case of problems involving conflicts between the metric and inch-pound units, the inch-pound units shall rule.
- 2. Pin numbers are for reference only.

FIGURE 1. Case outline(s) - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-97506
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Device types				01 and 02			
Case outline				Х			
Terminal number	Terminal symbol	Terminal number	Terminal symbol	Terminal number	Terminal symbol	Terminal number	Terminal symbol
1 2 3 4 5 6 7 8 9 10 11 12 13 14 15 16 17 18 19 20 21 22 23 24 25 26 27 28 29 30 31 32 33 34 35 36 37 38 39 40 41 42 43 44 44	RDDABCOOLS OF RECENT OF SELECTION OF SELECTI	45 46 47 48 49 51 52 53 55 55 56 61 62 63 64 66 67 77 77 77 77 77 77 77 77 77 77 77	GND RFSD1 RCLKD1 DRD1 TFSD1 TCLKD1 DTD1 VDD HBR DMAR1 DMAR2 SBTS BMSBCD SW GND MS0 MS1 MS2 MS3 VDD ADDR31 ADDR31 ADDR30 ADDR29 ADDR29 ADDR29 ADDR29 ADDR20 ADDR29 ADDR20 ADDR29 ADDR21 ADDR23 ADDR22 ADDR21 ADDR23 ADDR21 ADDR21 ADDR21 ADDR21 ADDR21 ADDR16 ADDR15 ADDR15 ADDR16 ADDR15 ADDR16 ADDR16 ADDR15 ADDR14 VDD	89 90 91 92 93 94 95 96 97 98 99 100 101 102 103 104 105 106 107 108 110 111 112 113 114 115 116 117 118 119 120 121 122 123 124 125 127 128 130 131 132	ADDR13 ADDR12 ADDR11 GND ADDR9 ADDR8 ADDR5 ADDR5 ADDR3 ADDR1 ADDR0 ADDR2 ADDR1 ADDR0 FLAGA0 FLAGGA0 FLAGGB2 FLAGGD2 FLAGGD2 FLAGGD2 FLAGGD2 FLAGD0 FLAGGA0 FLAGGD2 FLAGGD2 FLAGGD3 FLAGGD3 FLAGGD4 FLAGGD4 FLAGGD4 FLAGGD5 FLAGGD6 FLAGGD6 FLAGGD6 FLAGGD6 FLAGGD7 FLAGGA0 FLA	133 134 135 136 137 138 139 140 141 142 143 144 145 146 147 148 149 150 151 152 153 154 155 156 157 158 160 161 162 163 164 165 166 167 168 169 170 171 172 173 174 175 176	IRQB0 IRQB1 IRQB2 GND IRQC0 IRQC1 IRQC2 IRQC0 IRQC1 IRQCD1 IRQD1 IRQD1 IRQD1 IRQD1 IRQD1 IRQD1 IRQD1 IRQD1 IRQD2 VDD EBOOTA LBOOTBCD GND RESET RPBA GND LD4ACK LD4CLK LD4DAT1 LD4DAT2 LD4DAT3 VDD LD3ACK LD3CLK LD3CLK LD3DAT1 LD3DAT2 LD3DAT3 GND LD1ACK LD1CLK LD1DAT0 LD1DAT1 LD1DAT2 LD1DAT3 VDD LD1DAT1 LD1DAT3 VDD LD1DAT3 CAACK LD1CLK LD1DAT3 LC4ACK LC4CLK LC4CLK LC4DAT1

FIGURE 2. <u>Terminal connections</u>.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-97506
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Device types			01 and 02		
Case outline			Х		
Terminal number	Terminal symbol	Terminal number	Terminal symbol	Terminal number	Terminal symbol
177 178 179 180 181 182 183 184 185 186 187 188 189 190 191 192 193 194 195 196 197 198 199 200 201 202 203 204 205 206 207 208 209 210 211 212 213 214 215 216 217 218 219 220	LC4DAT2 LC4DAT3 GND LC3ACK LC3CLK LC3DAT1 LC3DAT2 LC3DAT3 VDD LC1ACK LC1CLK LC1DAT1 LC1DAT2 LC1DAT3 GND LB4ACK LB4CLK LB4DAT0 LB4DAT1 LB4DAT2 LB4DAT3 VDD LB3ACK LB3CLK LB3CLK LB3CLK LB3DAT1 LB3DAT2 LB3DAT3 GND LB3DAT1 LB1DAT2 LB1DAT3 CHB1DAT1 LB1DAT2 LB1DAT3 LA4ACK LA4CK LA4DAT0 LA4DAT1 LA4DAT2 LA4DAT3	221 222 223 224 225 226 227 228 229 230 231 232 233 234 235 236 237 238 239 240 241 242 243 244 245 246 247 248 249 250 251 252 253 254 255 256 257 258 259 260 261 262 263 264	GND LA3ACK LA3CLK LA3CLK LA3DAT1 LA3DAT2 LA3DAT3 V _{DD} LA1ACK LA1CLK LA1DAT0 LA1DAT1 LA1DAT2 LA1DAT3 GND DATA4 DATA5 DATA6 DATA5 DATA6 DATA7 GND DATA11 V _{DD} DATA11 DATA12 DATA13 DATA13 DATA14 DATA22 DATA11 DATA22 DATA11 DATA12 DATA11 DATA12 DATA12 DATA12 DATA13 DATA12 DATA13 DATA14 DATA15 GND DATA12 DATA13 DATA14 DATA15 GND DATA11 DATA12 DATA13	265 266 267 268 269 270 271 272 273 274 275 276 277 278 279 280 281 282 283 284 285 286 287 288 289 290 291 292 293 294 295 296 297 298 299 300 301 302 303 304 305 306 307 308	GND DATA24 DATA25 DATA26 DATA26 DATA27 VDD DATA28 DATA29 DATA30 DATA31 GND DATA33 DATA34 DATA35 VDD DATA36 DATA36 DATA37 DATA38 DATA37 DATA38 DATA39 GND DATA41 CLKIN GND DATA41 CLKIN GND DATA44 DATA45 DATA45 DATA45 DATA46 DATA47 GND BR1 BR2 BR3 BR4 BR5 BR6 PAGE VDD DMAGG1 DMAGC2 ACK

FIGURE 2. <u>Terminal connections</u> - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-97506
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000		REVISION LEVEL C	SHEET 28

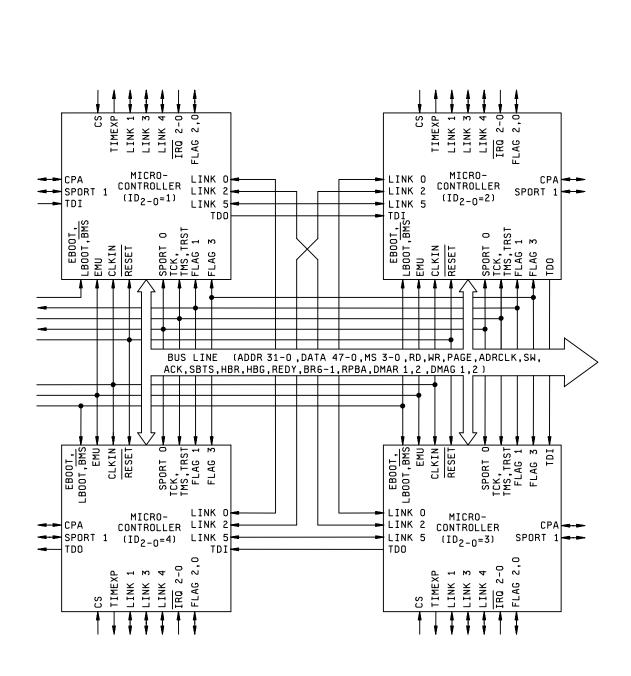


FIGURE 3. Block diagram.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-97506
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000		REVISION LEVEL C	SHEET 29

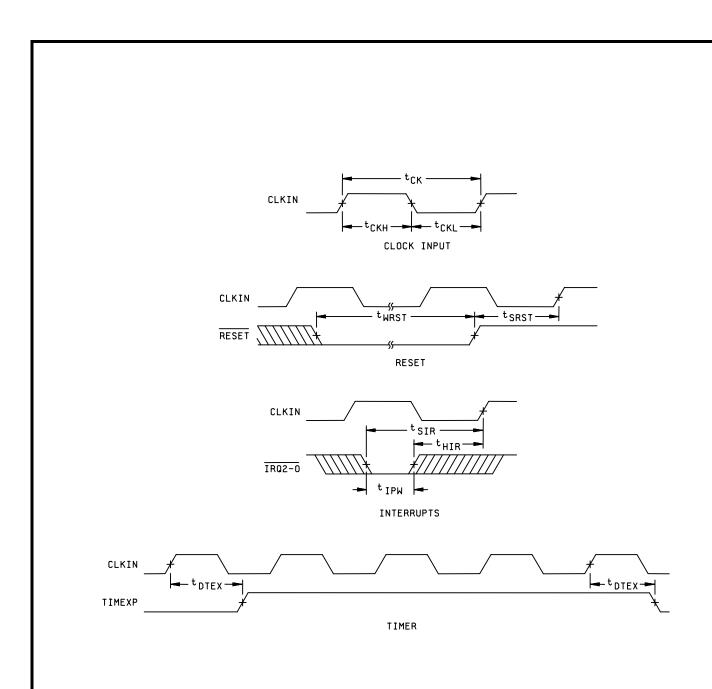
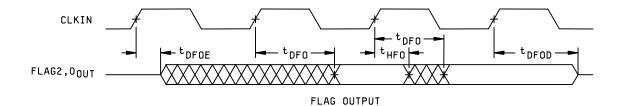
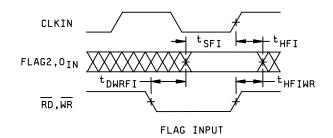


FIGURE 4. Timing waveforms.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-97506
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000		REVISION LEVEL C	SHEET 30





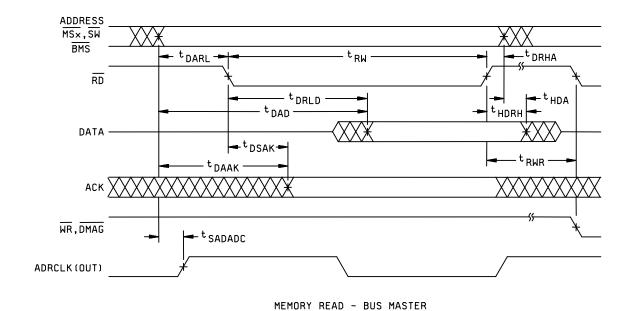


FIGURE 4. <u>Timing waveforms</u> - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-97506
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43216-5000		C	31

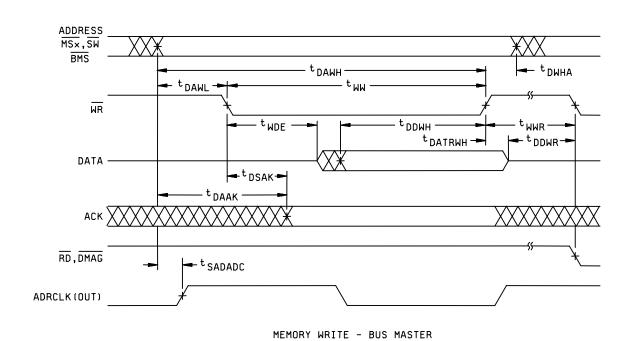


FIGURE 4. Timing waveforms - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-97506
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000		REVISION LEVEL C	32

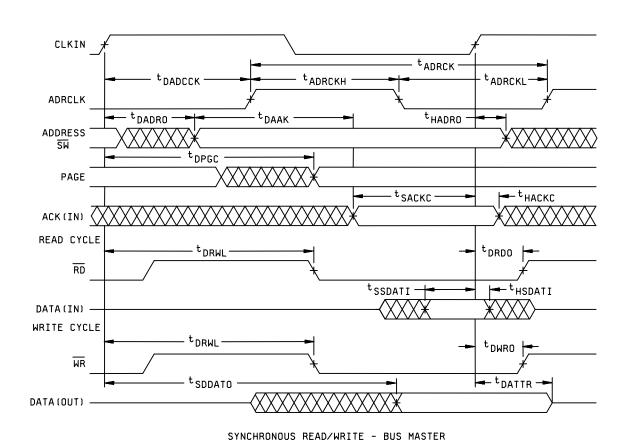


FIGURE 4. Timing waveforms - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-97506
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000		REVISION LEVEL C	SHEET 33

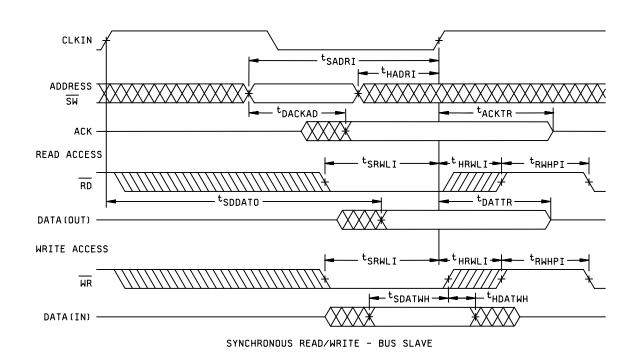


FIGURE 4. <u>Timing waveforms</u> - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-97506
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43216-5000		C	34

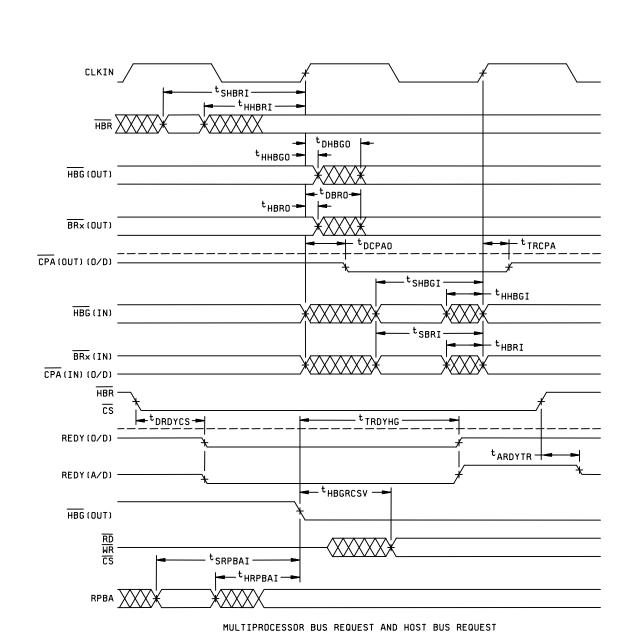


FIGURE 4. <u>Timing waveforms</u> - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-97506
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43216-5000		C	35

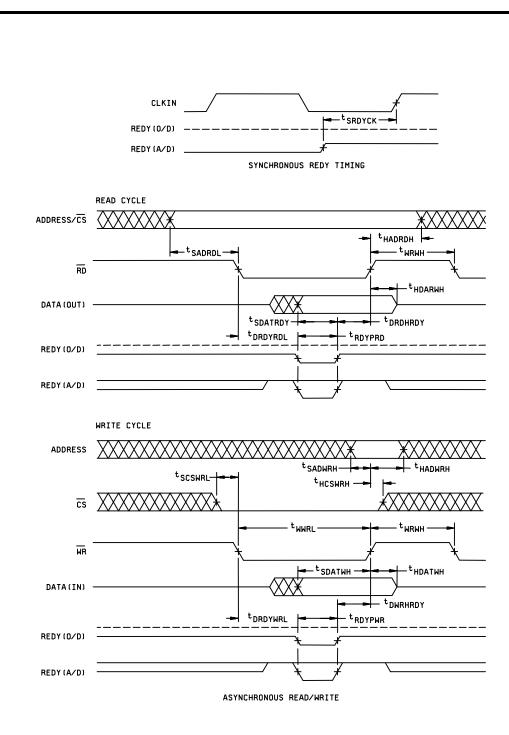


FIGURE 4. Timing waveforms - Continued.

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DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43216-5000		C	36

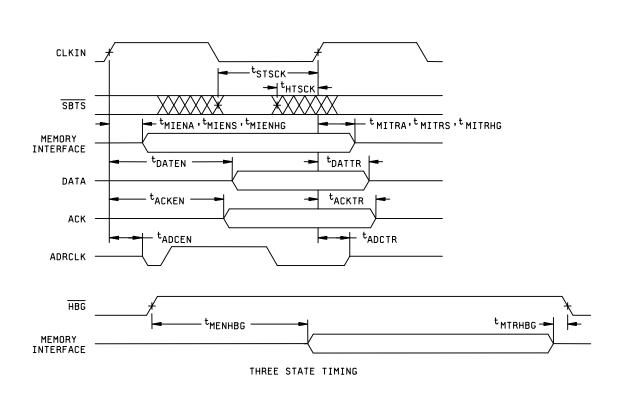


FIGURE 4. Timing waveforms - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-97506
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43216-5000		C	37

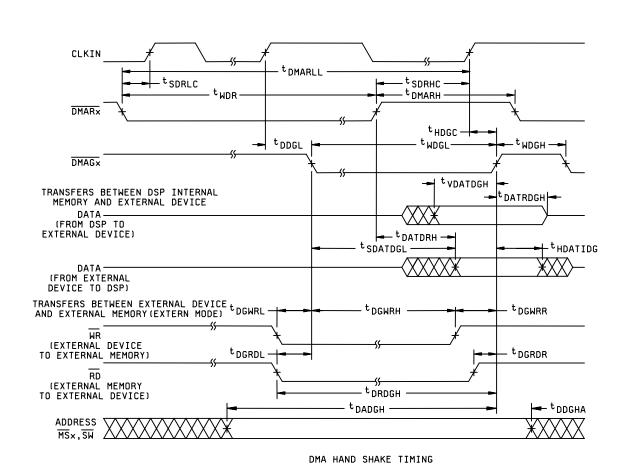
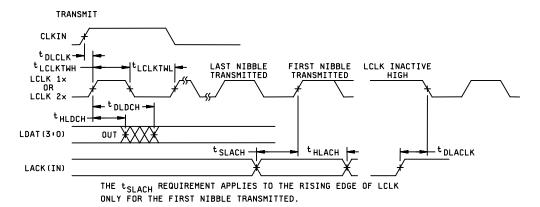
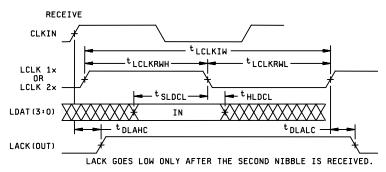
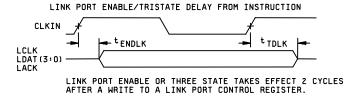


FIGURE 4. Timing waveforms - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-97506
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000		REVISION LEVEL C	SHEET 38







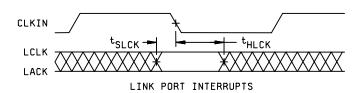
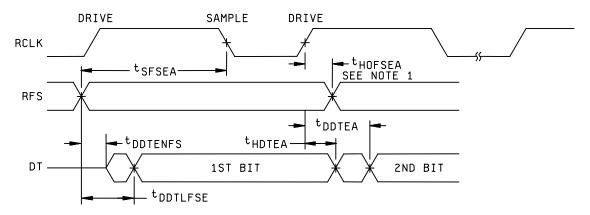


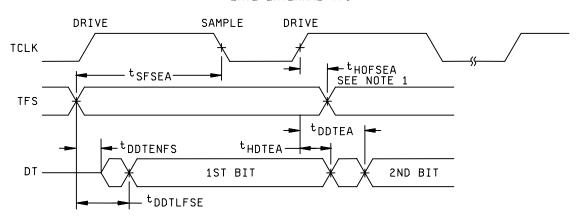
FIGURE 4. Timing waveforms - Continued.

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EXTERNAL RFS WITH MCE = 1, MFD = 0



LATE EXTERNAL TFS



EXTERNAL LATE FRAME SYNC

NOTE:

1. RFS hold after RCLK when MCS = 1, MFD = 0 is 0.5 ns minimum from drive edge. TFS hold after TCLK for late external TFS is 0.5 ns minimum from drive edge.

FIGURE 4. Timing waveforms - Continued.

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DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000		REVISION LEVEL C	SHEET 40

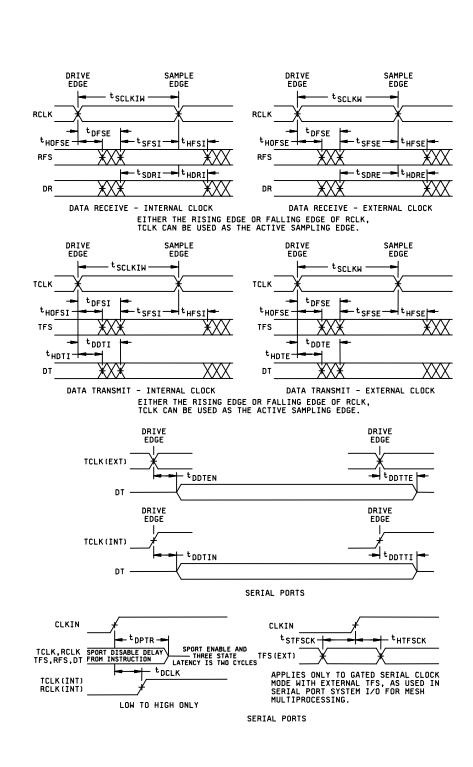


FIGURE 4. Timing waveforms - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-97506
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43216-5000		REVISION LEVEL C	SHEET 41

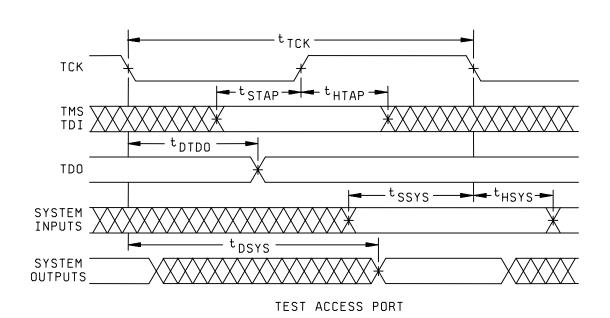
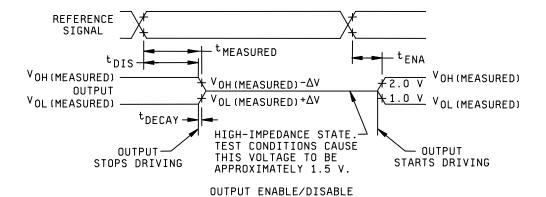
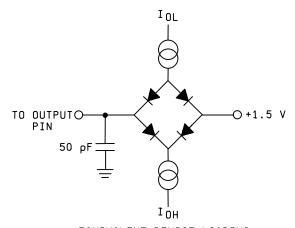


FIGURE 4. Timing waveforms - Continued.

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EQUIVALENT DEVICE LOADING FOR AC MEASUREMENTS (INCLUDES ALL FIXTURES)



VOLTAGE REFERENCE LEVELS FOR AC MEASUREMENTS (EXCEPT OUTPUT ENABLE/DISABLE)

FIGURE 4. Timing waveforms - Continued.

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TABLE II. Electrical test requirements.

MIL-PRF-38534 test requirements	Subgroups (in accordance with MIL-PRF-38534, group A test table)
Interim electrical parameters	Paragraph 4.2.b
Final electrical parameters	Paragraph 4.2.b*, 1, 2, 3, 7, 8, 9, 10, 11
Group A test requirements	1, 2, 3, 7, 8, 9, 10, 11
Group C end-point electrical parameters	1, 7, 9
End-point electrical parameters for radiation hardness assurance (RHA) devices	Not applicable

^{*} PDA applies to subgroup 1.

- 4.3 <u>Conformance and periodic inspections</u>. Conformance inspection (CI) and periodic inspection (PI) shall be in accordance with MIL-PRF-38534 and as specified herein.
 - 4.3.1 Group A inspection (CI). Group A inspection shall be in accordance with MIL-PRF-38534 and as follows:
 - a. Tests shall be as specified in table II herein.
 - b. Subgroups 4, 5, and 6 shall be omitted.
 - c. Subgroups 7 and 8 shall include verification of the functionality of the device.
 - 4.3.2 Group B inspection (PI). Group B inspection shall be in accordance with MIL-PRF-38534.
 - 4.3.3 Group C inspection (PI). Group C inspection shall be in accordance with MIL-PRF-38534 and as follows:
 - a. End-point electrical parameters shall be as specified in table II herein.
 - b. Steady-state life test, method 1005 of MIL-STD-883.
 - (1) Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to either DSCC-VA or the acquiring activity upon request. Also, the test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.
 - (2) T_C as specified in accordance with table I of method 1005 of MIL-STD-883.
 - (3) Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.
 - 4.3.4 Group D inspection (PI). Group D inspection shall be in accordance with MIL-PRF-38534.
 - 4.3.5 Radiation Hardness Assurance (RHA) inspection. RHA inspection is not currently applicable to this drawing.

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- 5. PACKAGING
- 5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-PRF-38534.
- 6. NOTES
- 6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.
- 6.2 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.
- 6.3 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-PRF-38534.
- 6.4 <u>Record of users</u>. Military and industrial users shall inform Defense Supply Center Columbus when a system application requires configuration control and the applicable SMD. DSCC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DSCC-VA, telephone (614) 692-0544.
- 6.5 <u>Comments</u>. Comments on this drawing should be directed to DSCC-VA, Post Office Box 3990, Columbus, Ohio 43216-5000, or telephone (614) 692-0536.
- 6.6 <u>Sources of supply</u>. Sources of supply are listed in MIL-HDBK-103 and QML-38534. The vendors listed in MIL-HDBK-103 and QML-38534 have submitted a certificate of compliance (see 3.7 herein) to DSCC-VA and have agreed to this drawing.

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TABLE III. Pin functions.

Terminal symbol	Type <u>1</u> /	Function
ADDR31-0	I/O/T	External Bus Address. (Common to all processors). The module outputs addresses for external memory and peripherals on these pins. In a multiprocessor system, the bus master outputs addresses for read/writes on the internal memory or IOP registers of slave processors. The module inputs addresses when a host processor or multiprocessing bus master is reading or writing the internal memory or IOP registers of internal processors.
DATA47-0	I/O/T	External Bus DATA. (Common to all processors). The module inputs and outputs data and instructions on these pins. 32-bit single-precision floating-point data and 32-bit fixed-point data is transferred over bits 47 - 16 of the bus. 40-bit extended-precision floating-point data is transferred over bits 47 - 8 of the bus. 16-bit short word data is transferred over bits 31 - 16 of the bus. In PROM boot mode, 8-bit data is transferred over bits 23 - 16. Pull-up resistors on unused DATA pins are not necessary.
 MS3-0	О/Т	Memory Select Lines. (Common to all processors). These lines are asserted (low) as chip selects for the corresponding banks of external memory. Memory bank size must be defined in the individual processors system control registers (SYSCON). The MS3-0 lines are decoded memory address lines that change at the same time as the other address lines. When no external memory access is occurring the MS3-0 lines are inactive; they are active, however, when a conditional memory access instruction is executed, whether or not the condition is true. MS0 can be used with the PAGE signal to implement a bank of DRAM memory (Bank 0). In multiprocessing system, the MS3-0 lines are output by the bus master.
RD	I/O/T	Memory Read Strobe. (Common to all processors). This pin is asserted (low) when the processor reads from external devices or when the internal memory of internal processors is being accessed. External devices (including other processors) must assert RD to read from the processors internal memory. In a multiprocessing system, RD is output by the bus master and is input by all other processors.
WR	I/O/T	Memory Write Strobe. (Common to all processors). This pin is asserted (low) when the processor writes from external devices or when the internal memory of internal processors is being accessed. External devices (including other processors) must assert WR to write from the processors internal memory. In a multiprocessing system, WR is output by the bus master and is input by all other processors.
PAGE	О/Т	DRAM Page Boundary. (Common to all processors). The module asserts this pin to signal that an external DRAM page boundary has been crossed. DRAM page size must be defined in the individual processor's memory control register (WAIT). DRAM can only be implemented in external memory Bank 0; the PAGE signal can only be activated for Bank 0 accesses. In a multiprocessing system, PAGE is output by the bus master.
ADRCLK	O/T	Clock Output Reference. (Common to all processors). In a multiprocessing system, ADRCLK is output by the bus master.
SW	I/O/T	Synchronous Write Select. (Common to all processors). This signal is used to interface the processor to synchronous memory devices (including other processors). The module asserts SW (low) to provide an early indication of an impending write cycle, which can be aborted if WR is not later asserted (e.g. in a conditional write instruction). In a multiprocessing system, SW is output by the bus master and is input by all other processors to determine if the multiprocessor memory access is a read or write. SW is asserted at the same time as the address output. A host processor using synchronous writes must assert this pin when writing to module.

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Terminal symbol	Type <u>1</u> /	Function	
ACK	I/O/S	Memory Acknowledge. (Common to all processors). External devices can deassert ACK (low) to add wait states to an external memory access. ACK is used by I/O devices, memory controllers, or other peripherals to hold off completion of an external memory access. The module deasserts ACK, as an output, to add wait states to a synchronous access of its internal memory. In a multiprocessing system, a slave processor deasserts the bus master's ACK input to add wait state(s) to an access of its internal memory. The bus master has a keeper latch on its ACK pin that maintains the input at the level it was last driven to.	
SBTS	I/S	Suspend Bus Three State. (Common to all processors). External devices can assert SBTS (low) to place the external bus address, data, selects, and strobes in a high impedance state for the following cycle. If the module attempts to access external memory while SBTS is asserted, the processor will halt and the memory access will not be complete until SBTS is deasserted. SBTS should only be used to recover from the host processor/ the module deadlock, or used with a DRAM controller.	
HBR	I/A	Host Bus Request. (Common to all processors). Mu <u>st be</u> asserted by a host processor to request control of the module's external bus. When HBR is asserted in a <u>multiprocessor</u> system, the processor that is bus master will relinquish the bus and assert HBG. To relinquish the bus, <u>the</u> processor places the address, data, select, and strobe lines in a high impedance state. HBR has priority over all processor bus requests (BR 6-1) in a multiprocessing system.	
HBG	I/O	Host Bus Grant. (Common to all processors). Acknowledges an HBR bus request, indicating that the host processor may take control of the external bus. HBG is asserted (held low) by the module until HBR is released. In a multiprocessing system, HBG is output by the processor bus master and is monitored by all others.	
CSA	I/A	Chip Select. Asserted by host processor to select processor-A.	
 CSB	I/A	Chip Select. Asserted by host processor to select processor-B.	
csc	I/A	Chip Select. Asserted by host processor to select processor-C.	
CSD	I/A	Chip Select. Asserted by host processor to select processor-D.	
REDY (O/D)	0	Host Bus Acknowledge. (Common to all processors). The module deasserts REDY (low) to add wait states to an asynchronous access of its internal memory or IOP registers by a host Open drain output (O/D) by default; can be programmed in ADREDY bit of SYS <u>ON</u> register of individual processors to be active drive (A/D). REDY will only be output if the CS and HBR inputs are asserted.	
BR6-1	I/O/S	Multiprocessing Bus Requests. (Common to all processor). Used by multiprocessing processors to arbitrate for bus mastership. A processor only drives its own BRx line (corresponding to the value of its ID2-0 inputs) and monitors all others. In a multiprocessing system with less than six processors the unused BRx pins should be pulled high; BR4-1 must not be pulled high or low because they are outputs.	

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Terminal symbol	Type <u>1</u> /	Function	
RPBA	I/S	Rotating Priority Bus Arbitration Select. (Common to all processors). When RPBA is high, rotating priority for multiprocessor bus arbitration is selected. When RPBA is low, fixed priority is selected. This signal is a system configuration selection that must be set to the same value on every processor. If the value of RPBA is changed during system operation, it must be changed in the same CLKIN cycle on every processor.	
CPAy (O/D)	I/O	Core Priority Access (y=processor-A, -B, -C, -D). Asserting its CPA pin allows the core processor of a <u>bus</u> slave to interrupt background DMA transfers and gain access to the external bus. CPA is an open d <u>rain</u> output that is connected to all processors in the system, if this function is <u>requi</u> red. The CPA pin of each internal processor is brought out individually. The CPA pin ha <u>s an</u> internal 5 kohm pull-up resistor. If core access priority is not required in a system, the CPA pin should be left unconnected.	
DT0	O/T	Data Transmit (Common serial ports 0 to all processors, TDM). DT pin has four parallel 50 kohm internal pull-up resistors.	
DR0	I	Data Receive (Common serial ports 0 to all processors, TDM). DR pin has four parallel 50 kohm internal pull-up resistors.	
TCLK0	I/O	Transmit Clock (Common serial ports 0 to all processors, TDM). TCLK pin has four parallel 50 kohm internal pull-up resistors.	
RCLK0	I/O	Receiver Clock (Common serial ports 0 to all processors, TDM). RCLK pin has four parallel 50 kohm internal pull-up resistors.	
TFS0	I/O	Transmit Frame Sync (Common serial ports 0 to all processors, TDM).	
RFS0	I/O	Receiver Frame Sync (Common serial ports 0 to all processors, TDM).	
DTy1	O/T	Data Transmit (Serial port 1 individual from processor-A, -B, -C, -D). Each DT pin has a 50 kohm internal pull-up resistor.	
DRy1	I	Data Receive (Serial port 1 individual from processor-A, -B, -C, -D). Each DR pin has a 50 kohm internal pull-up resistor.	
TCLKy1	I/O	Transmit Clock (Serial port 1 individual from processor-A, -B, -C, -D). Each TCLK pin has a 50 kohm internal pull-up resistor.	
RCLKy1	I/O	Receive Clock (Serial port 1 individual from processor-A, -B, -C, -D). Each RCLK pin has a 50 kohm internal pull-up resistor.	
TFSy1	I/O	Transmit Frame Sync (Serial port 1 individual from processor-A, -B, -C, -D).	
RFSy1	I/O	Receive Frame Sync (Serial port 1 individual from processor-A, -B, -C, -D).	
FLAGy0	I/O/A	Flag Pins, 2/. (FLAG0 individual from processor-A, -B, -C, -D). Each is configured via control bits as either an input or output. As an input, it can be tested as a condition. As an output, it can be used to signal external peripherals.	

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Terminal symbol	Type <u>1</u> /	Function	
FLAG1	I/O/A	Flag Pins, 2/. (FLAG1 common to all processors). Configured by control bits internal to individual processors as either an input or output. As an input it can be tested as a condition. As an output, it can be used to signal external peripherals.	
FLAGy2	I/O/A	FLAG Pins, 2/. (FLAG2 individual from processor-A, -B, -C, and -D). Each is configured by control bits as either an input or output. As an input, it can be tested as a condition. As an output, it can be used to signal external peripherals.	
ĪRQy2-0	I/A	Interrupt Request Lines. (Individual \overline{IRQ} 2-0 from y = processor-A, -B, -C, -D). May be either edge-triggered or level-sensitive.	
 DMAR1	I/A	DMA Request 1 (DMA Channel 7). Common to processor-A, -B, -C, -D.	
DMAR2	I/A	DMA Request 1 (DMA Channel 8). Common to processor-A, -B, -C, -D.	
DMAG1	O/T	DMA Grant 1 (DMA Channel 7). Common to processor-A, -B, -C, -D.	
DMAG2	O/T	DMA Grant 2 (DMA Channel 8). Common to processor-A, -B, -C, -D.	
LyxCLK	I/O	Link Port Clock (y = processor-A, -B, -C, -D; x = Link Ports 1, 3, 4), 3/. Each LyxCLK pin has a 50 kohm internal pull-up resistor which is enabled or disabled by the LPDRD bit of the LCOM register, of the processor.	
LyxDAT3-0	I/O	Link Port Data (y = processor-A, -B, -C, -D; x = Link Ports 1, 3, 4), 3/. Each LyxDAT pin ha a 50 kohm internal pull-up resistor which is enabled or disabled by the LPDRD bit of the LCOM register, of the processor.	
LyxACK	I/O	Link Port Acknowledge (y = processor-A, -B, -C, -D; x = Link Ports 1, 3, 4), 3/. Each LyxACK pin has a 50 kohm internal pull-up resistor which is enabled or disabled by the LPDRD bit of the LCOM register, of the processor.	
BMSA	I/O/T <u>4</u> /	Boot Memory Select. Output: Used as chip select for boot <u>EPROM</u> devices (when EBOOTA = 1, LBOOTA = 0). In a multiprocessor system, BMS is output by the bus mast Input: When low, indicates that no booting will occur and that processor-A will begin executing instructions from external memory. See table in note 4. This input is a system configuration selection which should be hardwired.	
EBOOTA	ı	EPROM Boot Select. (processor-A) When EBOOTA is high, processor-A is configured for booting from an 8-bit EPROM. When EBOOTA is low, the LBOOTA and BMSA inputs determine booting mode for processor-A. See table in note 4. This signal is a configuration selection which should be hardwired.	
LBOOTA	I	Link Boot. When LBOOTA is high, processor-A is configured for link port booting. When LBOOTA is low, processor-A is configured for host processor booting or no booting. See table in note 4. This signal is a system configuration selection which should be hardwired.	

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Terminal symbol	Type <u>1</u> /	Function	
EBOOTBCD	I	EPROM Boot Select. (Common to processor-B, -C, -D). When EBOOTBCD is high, processor-B, -C, -D are configured for booting from an 8-bit EPROM. When EBOOTBCD is low, the LBOOTBCD and BMSBCD inputs determine booting mode for processor-B, -C, and -D. See table in note 4. This signal is a system configuration selection which should be hardwired.	
LBOOTBCD	I	LINK Boot. (Common to processor-B, -C, -D). When LBOOTBCD is high, processor-B, -C, -D are configured for link port booting. When LBOOTBCD is low, multiprocessor-B, -C, -D are configured for host processor booting or no booting. See table in note 4. This signal is a system configuration selection which should be hardwired.	
BMSBCD	I/O/T <u>4</u> /	Boot Memory Select. Output: Used as chip select for boot EPROM devices (when EBOOTBCD = 1, LBOOTBCD = 0). In a multiprocessor system, BMS is output by the bus master. Input: When low, indicates that no booting will occur and that processor-B, -C, -D will begin executing instructions from external memory. See table in note 4. This input is a system configuration selection which should be hardwired.	
TIMEXPy	0	Timer Expired. (Individual TIMEXP from $y = processor-A, -B, -C, -D$). Asserted for four cycles when the timer is enabled and t_{count} decrements to zero.	
CLKIN	I	Clock In. (Common to all processors). External clock input to the module. The instruction cycle rate is equal to CLKIN. CLKIN may not be halted, changed, or operated below the minimum specified frequency.	
RESET	I/A	Module Reset. (Common to all processors). Resets the module to a known state. This input must be asserted (low) at power-up.	
TCK	I	Test Clock (JTAG). (Common to all processors). Provides an asynchronous clock for JTAG boundary scan.	
TMS	I/S	Test Mode Select (JTAG). (Common to all processors). Used to control the test state machine. TMS has four parallel 20 kohm internal pull-up resistors.	
TDI	I/S	Test Data Input (JTAG). Provides serial data for the boundary scan logic chain starting at processor-A. TDI has a 20 kohm pull-up resistor.	
TDO	0	Test Data Output (JTAG). Serial scan output of the boundary scan chain path, from processor-D.	
TRST	I/A	Test Reset (JTAG). Common to all processors). Resets the test state machine. TRST must be asserted (pulsed low) after power-up or held low for proper operation of the module. TRST has four parallel 20 kohm internal pull-up resistors.	
EMU(O/D)	0	Emulation Status. (Common to all processors). Pin 118 must be connected to the module's target board test connector only.	
V_{DD}	Р	Power Supply. Nominally +5.0 V dc (26 pins).	
GND	G	Power supply returns. The lid to the module is electrically connected to GND.	

See footnotes on the following sheet.

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NOTES:

1/ Type: A = asynchronous, A/D = active drive, G = ground, I = input, O = output, O/D= open drain, P = power supply, S = synchronous, T = three state (when SBTS is asserted, or when the module is a bus slave).

Inputs identified as synchronous (S) must meet timing requirements with respect to CLKIN (or with respect to TCK for TMS, TDI). Inputs identified as asynchronous (A) can be asserted asynchronously to CLKIN(or to TCK for TRST).

Unused inputs should be tied or pulled to VDD or GND, except for ADDR31-0, DATA47-0, FLAG2,0, \overline{SW} , and inputs that have internal pull-up or pull-down resistors (CPA, ACK, DTx, DTy, TCLKx, RCLKx, LxDAT3-0, LxCLK, LxACK, TMS, and TDI) - these pins can be left floating. These pins have a logic-level hold circuit that prevents the input from floating internally.

ID pins are hardwired internally.

- 2/ FLAG3 is connected internally, common to processor-A, -B, -C, and -D.
- 3/ LINK PORTS 0, 2, and 5 are connected internally between processors -A, -B, -C, and -D.
- 4/ Three statable only in EPROM boot mode (when BMS is an output).

EBOOT	LBOOT	BMS	Booting Mode
1	0	output	EPROM (connect BMS to EPROM chip select)
0	0	1 (input)	Host processor
0	1	1 (input)	Link port
0	0	0 (input)	No booting. Processor executes from external memory.
0	1	0 (input)	Reserved
1	1	x (input)	Reserved

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STANDARD MICROCIRCUIT DRAWING BULLETIN

DATE: 03-03-31

Approved sources of supply for SMD 5962-97506 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38534 during the next revisions. MIL-HDBK-103 and QML-38534 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DSCC-VA. This bulletin is superseded by the next dated revisions of MIL-HDBK-103 and QML-38534.

Standard microcircuit drawing PIN <u>1</u> /	Vendor CAGE number	Vendor similar PIN <u>2</u> /
5962-9750601HXC	34031	AD14060BF/QML-4
5962-9750602HXC	34031	AD14060TF/QML-4

- 1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the Vendor to determine its availability.
- <u>Oution</u>. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

Vendor CAGE number Vendor name and address

34031

Analog Devices, Incorporated 7910 Triad Center Drive Greensboro, NC 27409-9605

Point of contact: Assembled Products Division

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